



武汉大学

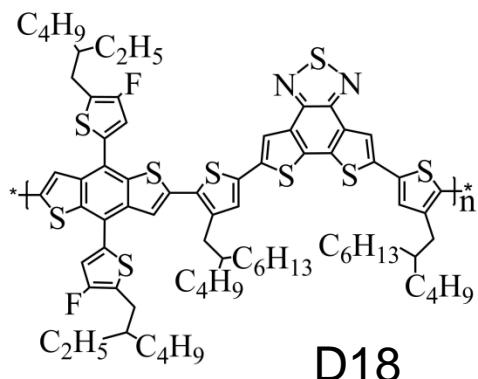
Optoelectronic Characterization and Device Considerations of Next-generation Solution-processed Semiconductors

Qianqian Lin

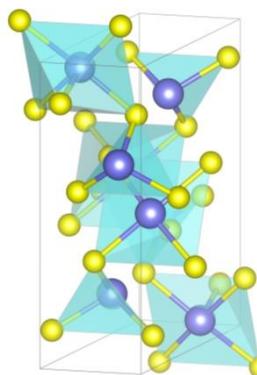
Email: q.lin@whu.edu.cn

School of Physics and Technology, Wuhan University

Organic semiconductors

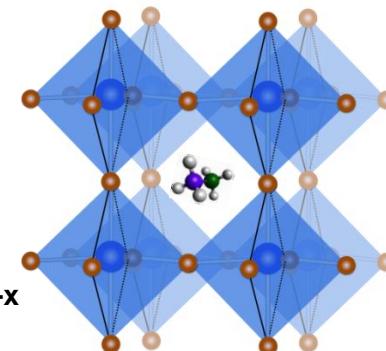


Chalcogenides



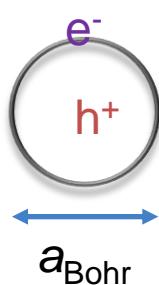
Bi₂S₃, AgBiS₂, NaBiS₂
Sb₂S₃, AgSbS₂,
Sb₂(S,Se)₃
PbS, AgInS₂, Se, Te_xSe_{1-x}

Hybrid perovskites



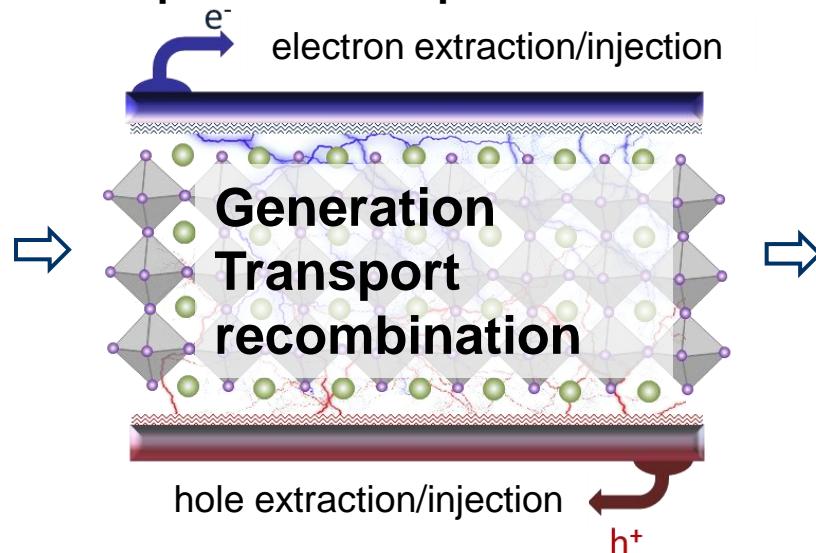
Opto-electronic characterization & devices

Optoelectronic properties



$n, k, \sigma,$
 $\epsilon, \mu, N_A,$
 $N_D, \tau, \gamma,$
 $L_D, E_b,$
 a_{Bohr}

Optoelectronic processes



Device performance

Solar cells:

$V_{\text{oc}}, J_{\text{sc}}, \text{FF}, \text{PCE}$

Photodetectors:

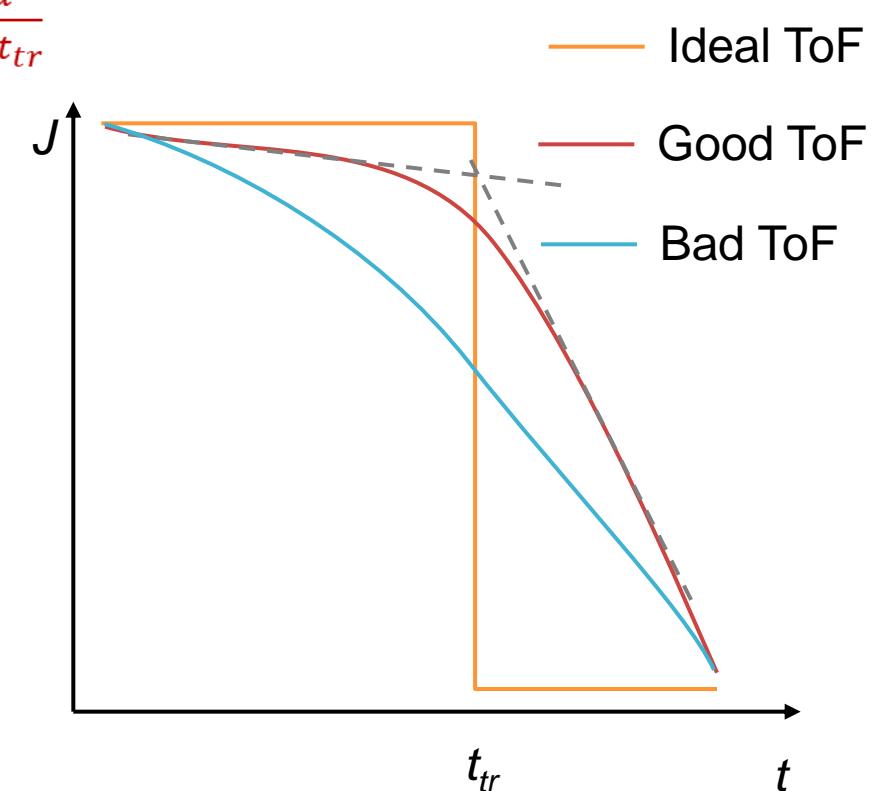
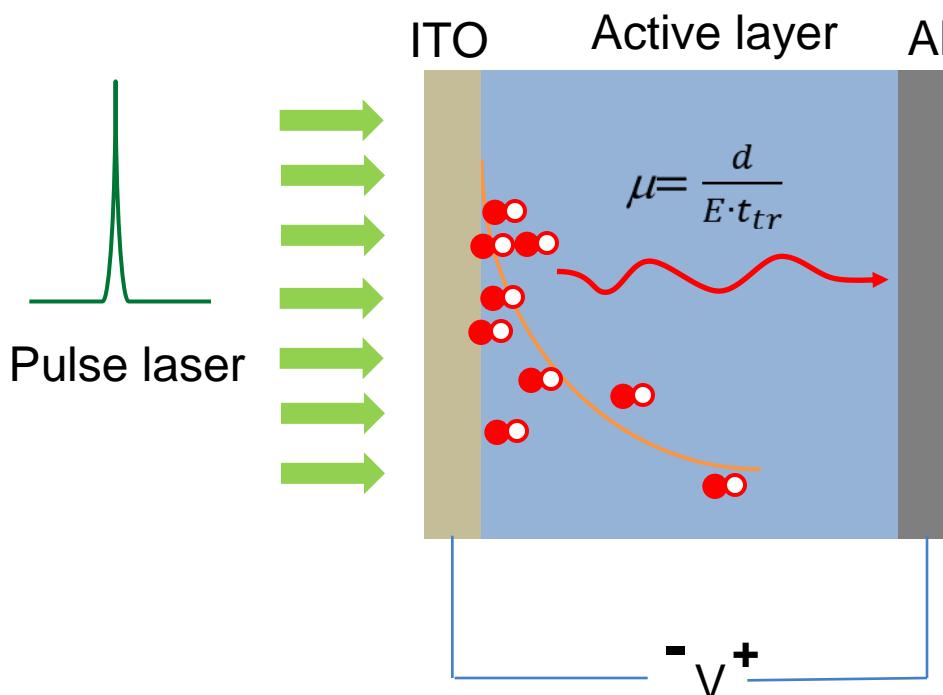
$D, \text{LDR}, f_{-3\text{dB}}, J_{\text{noise}}$

LEDs:

Color, L , QE, t_r ,

Time of flight (ToF)

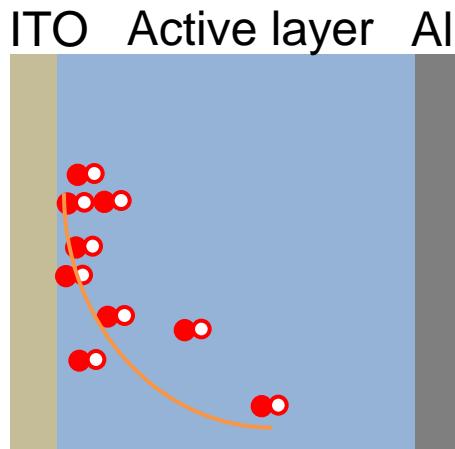
$$v = d/t_{tr} \quad \mu = \frac{d}{E \cdot t_{tr}}$$



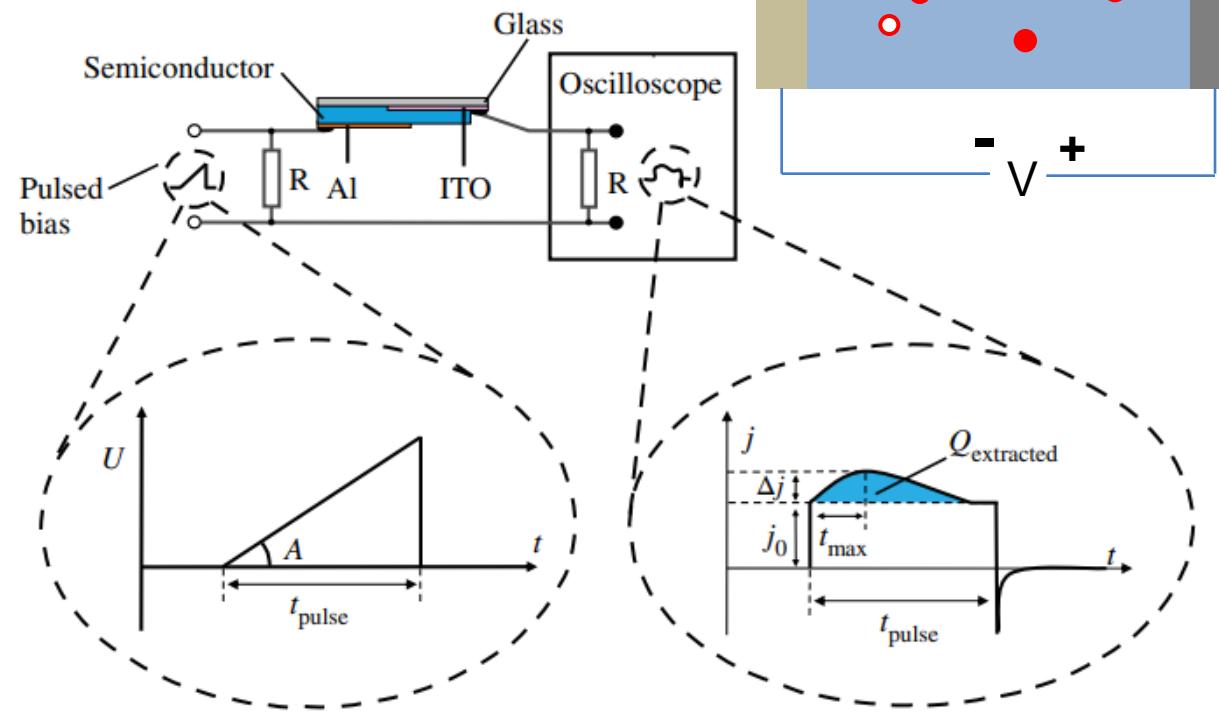
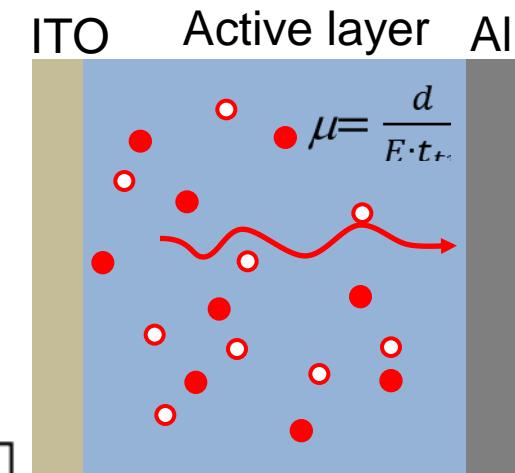
- Carrier generation need to be on the surface with a thick junction
- Mobility is highly dispersive for disordered materials
- Field dependent
- High voltage bias may cause degradation

Charge extraction by linearly increasing voltage (photo-CELIV)

$$v = d/t_{tr} \quad \mu = \frac{d}{E \cdot t_{tr}}$$

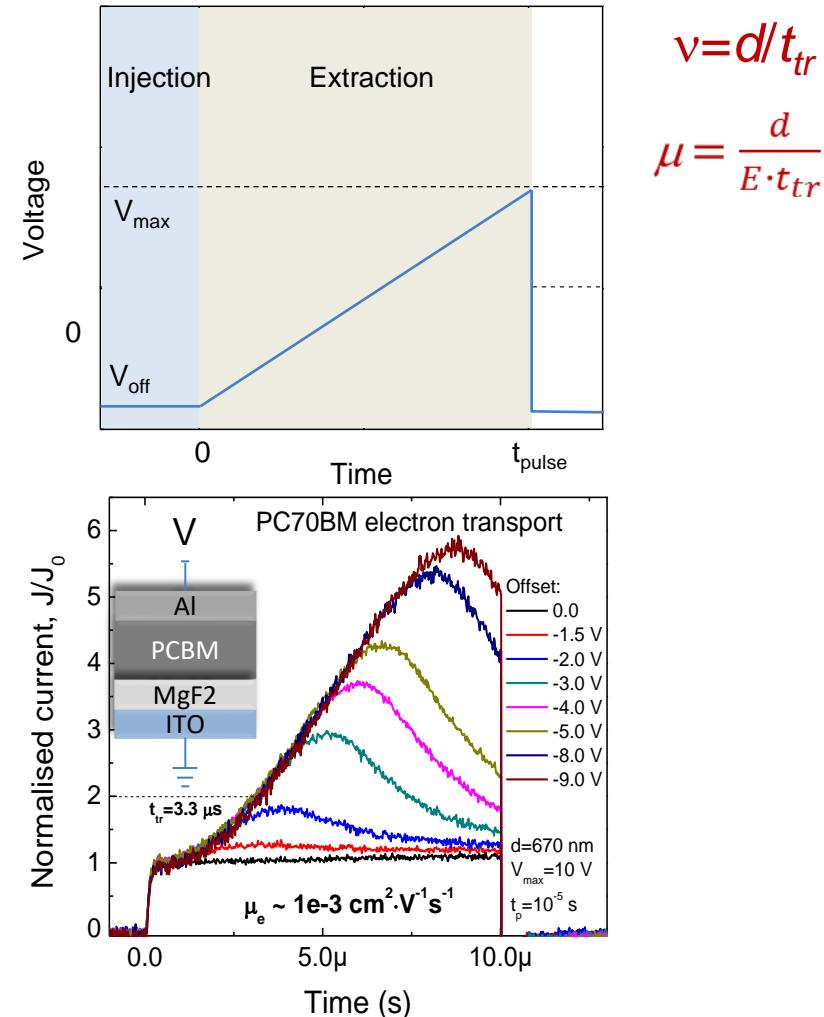
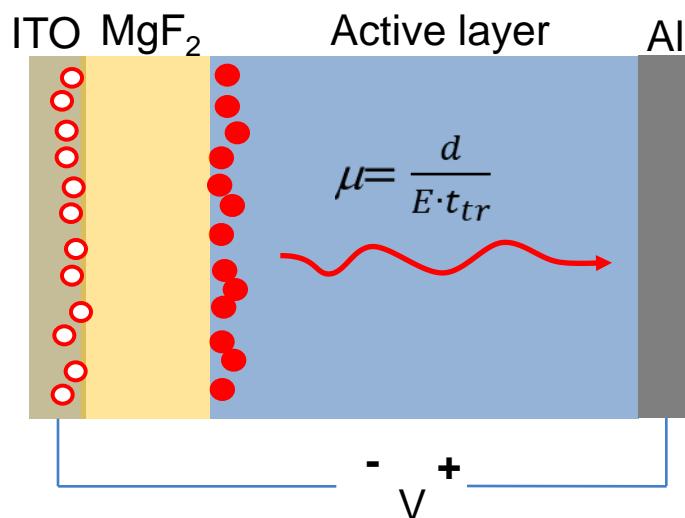
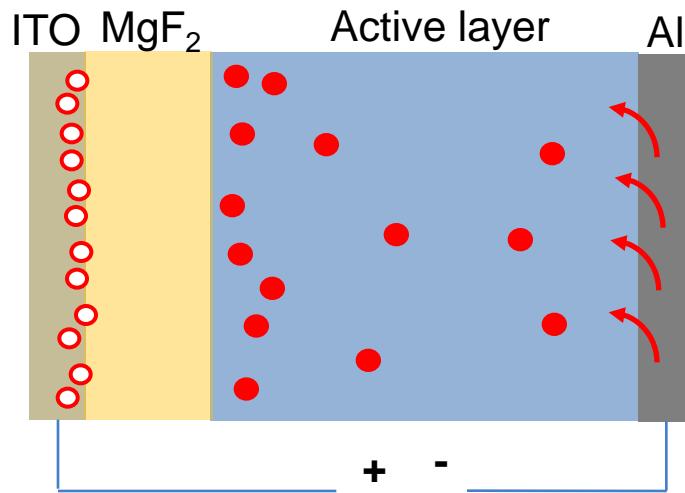


Charge extraction



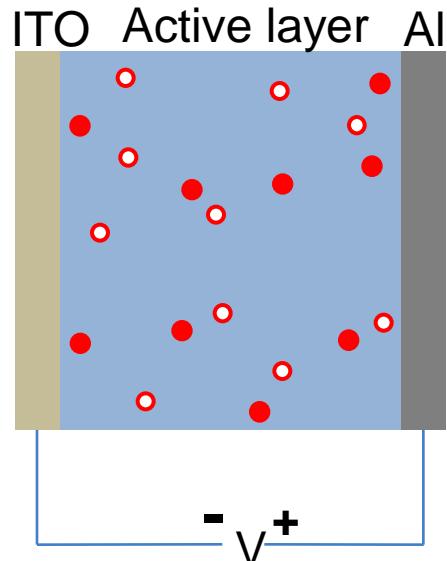
- Mixed mobility
- Photogeneration
- Recombination

Metal-insulator-Semiconductor charge extraction by linearly increasing voltage (MIS-CELIV)



- ✓ Measure electron and hole mobility separately
- ✓ Reduce dispersive charge transport

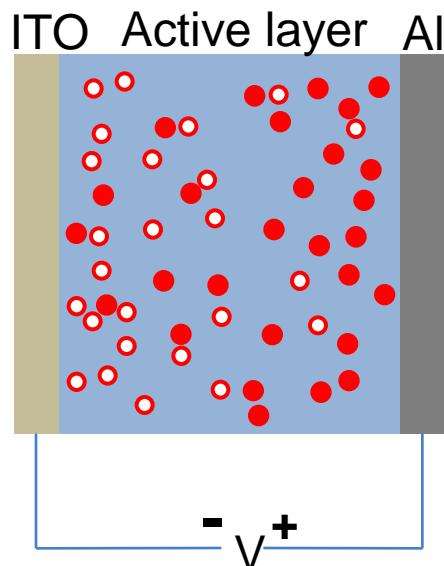
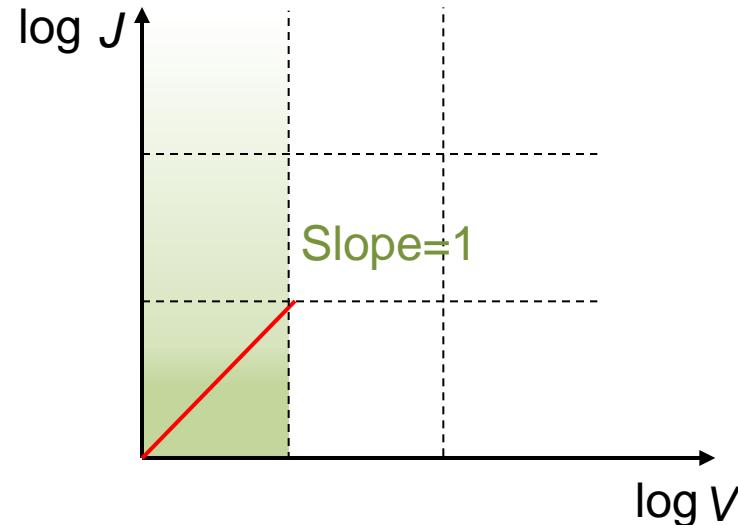
Space charge limited current (SCLC)



$$\sigma = e \cdot N \cdot \mu$$

$$E = \frac{V}{d}$$

$$J = E \cdot \sigma = \frac{V \cdot e \cdot N \cdot \mu}{d}$$

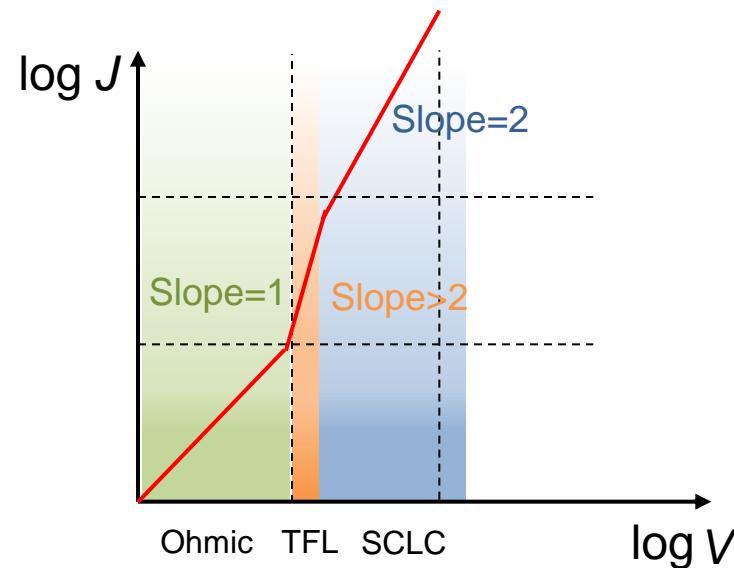


$$Q = C \cdot V$$

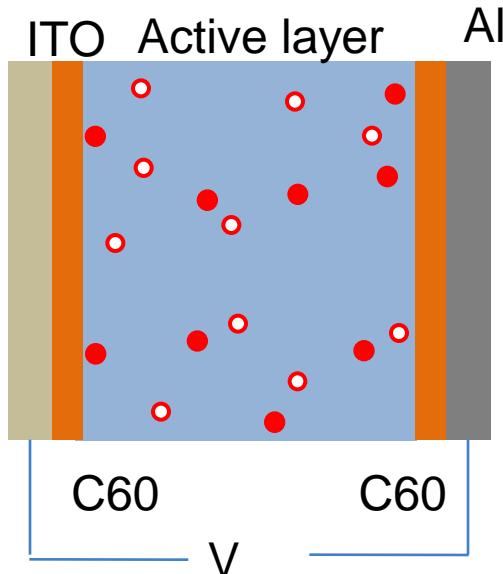
$$\mu = \frac{d}{E \cdot t_{tr}}$$

$$J = \frac{Q}{t_{tr}} = \frac{C \cdot V}{t_{tr}}$$

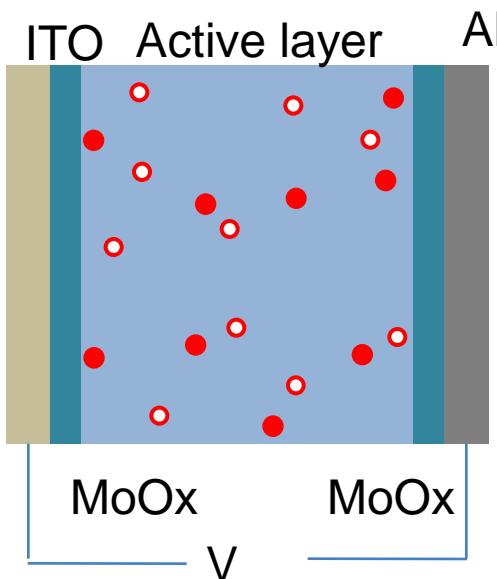
$$J \propto \frac{\epsilon \cdot \mu \cdot V^2}{d^3}$$



Electron only device

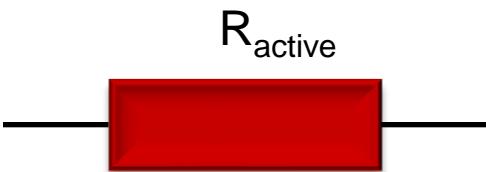


Hole only device



- Ohmic contact
- Trap states
- Conductivity
- Series resistance

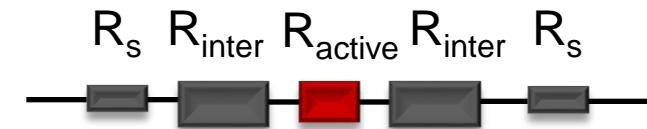
Ideal SCLC



Real SCLC



Non-ideal SCLC



Light intensity dependent photocurrent

Deviation from linearity

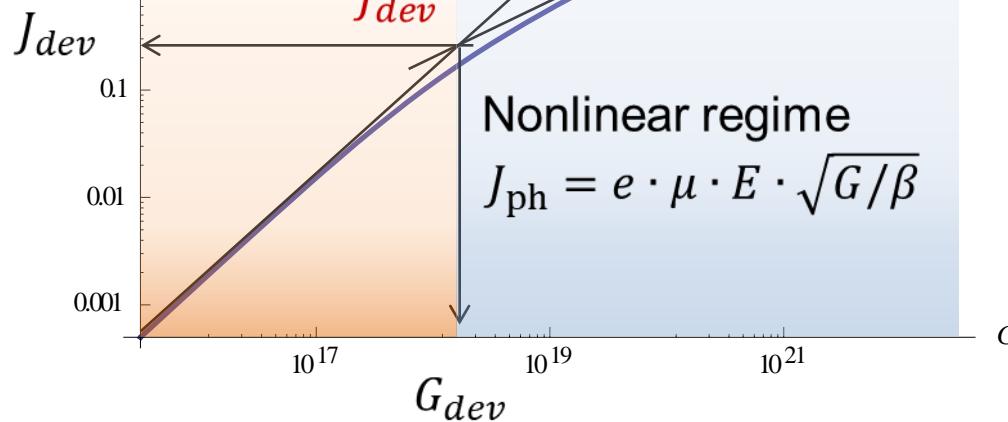
Linear regime

$$J_{ph} = e \cdot \mu \cdot E \cdot \frac{G}{\frac{1}{t_{tr}} + \frac{1}{\tau_m}}$$

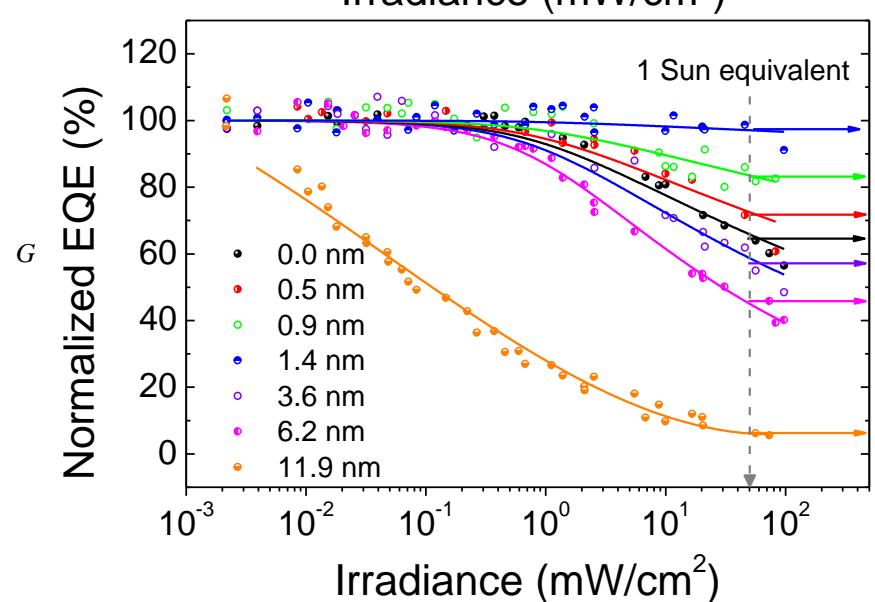
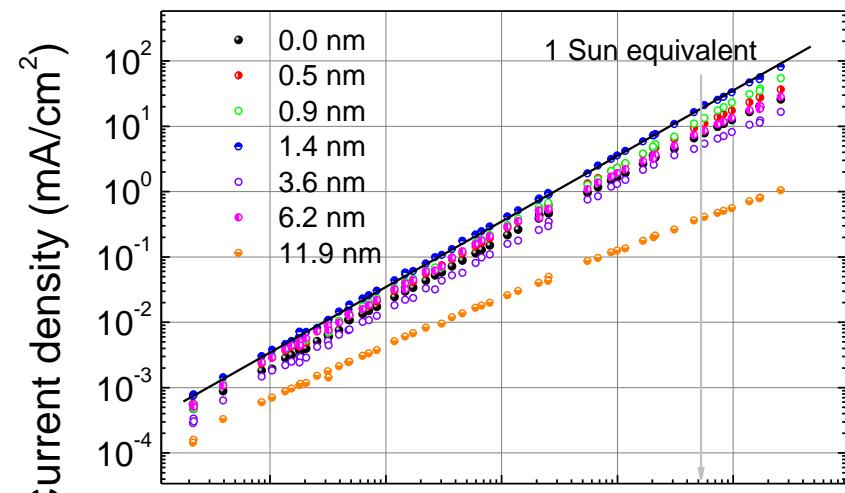
$$t_{tr} = \frac{C \cdot V}{J_{dev}}$$

Nonlinear regime

$$J_{ph} = e \cdot \mu \cdot E \cdot \sqrt{G / \beta}$$



This is important in Linear Dynamic Range of photodetectors and also Power Conversion Efficiency of solar cells.



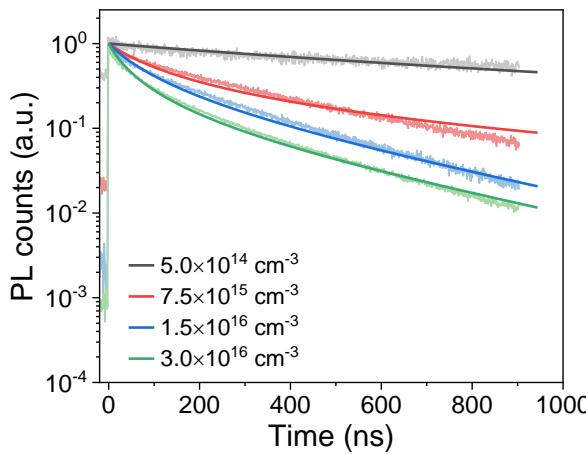
- Time-resolved Photoluminescence:

Time-correlated single photon counting (TCSPC): high time resolution, poor spectra;

Gated intensified CCD (iCCD) spectroscopy: excellent spectra, poor time resolution;

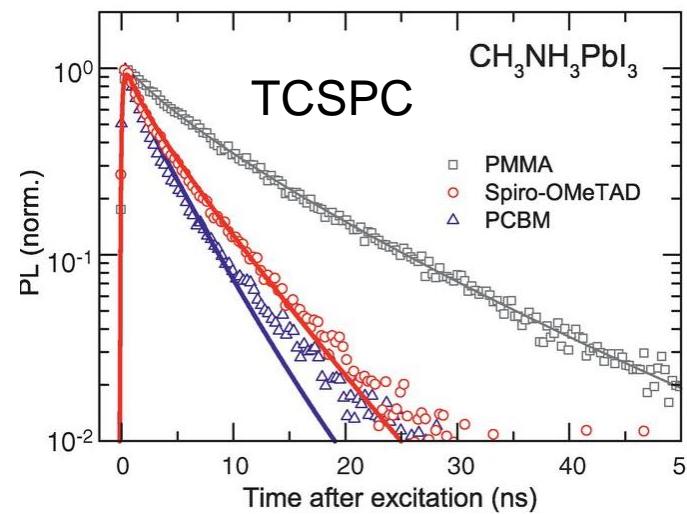
Streak camera: excellent spectra, fast response, high price;

Femtosecond photoluminescence upconversion (fs PLUC): sub-picosecond resolution (100 fs), very low detectivity.



$$\frac{dn}{dt} = G - k_1 n - k_2 n^2 - k_3 n^3$$

Lifetime, recombination rates, diffusion length



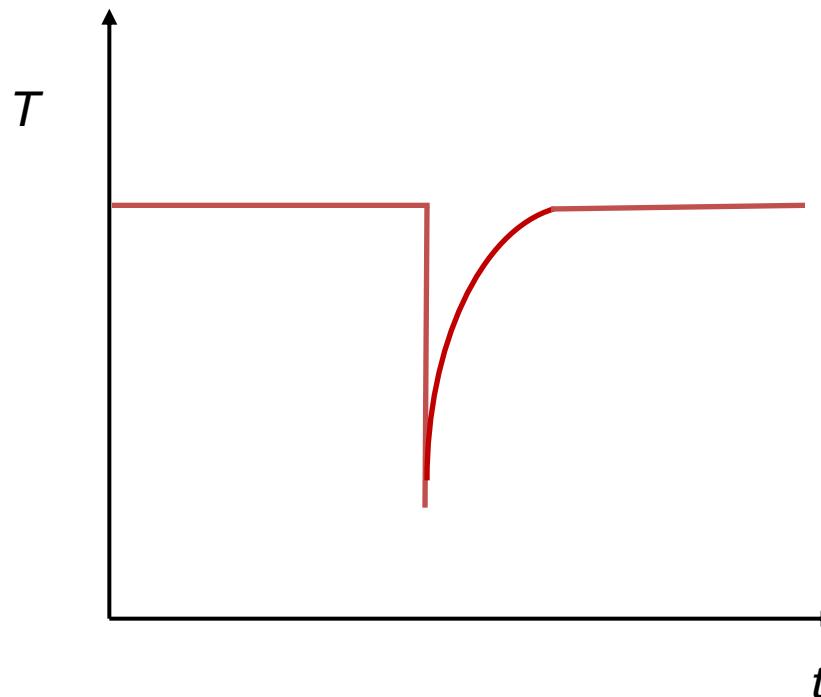
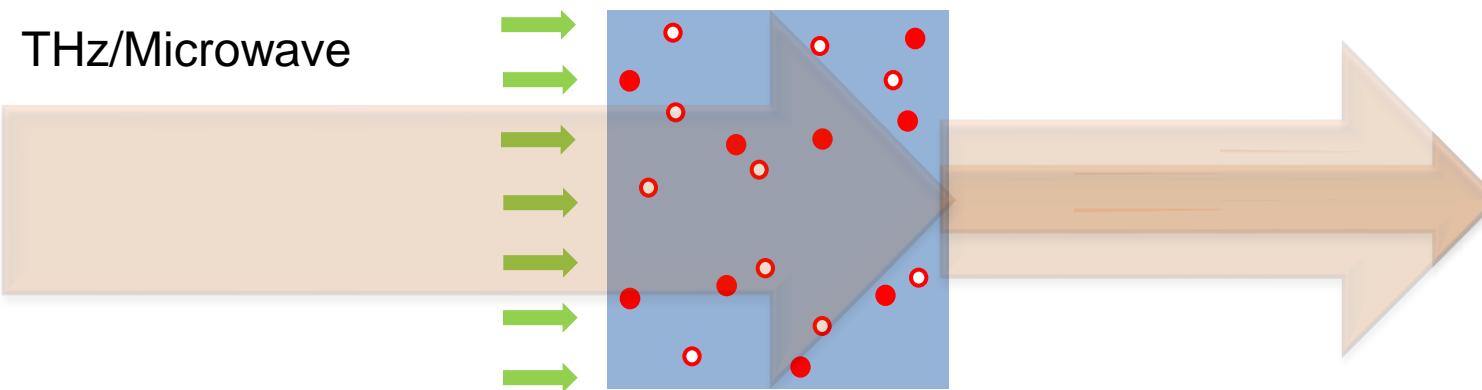
$$D = \mu \frac{kT}{e}$$

$$L = \sqrt{D\tau}$$

$$\frac{\partial n(x,t)}{\partial t} = D \frac{\partial^2 n(x,t)}{\partial x^2} - k(t)n(x,t)$$

Stranks S D et al. **Science**, 342(6156): 341-344 (2013).

- Time-resolved microwave conductivity (TRMC):

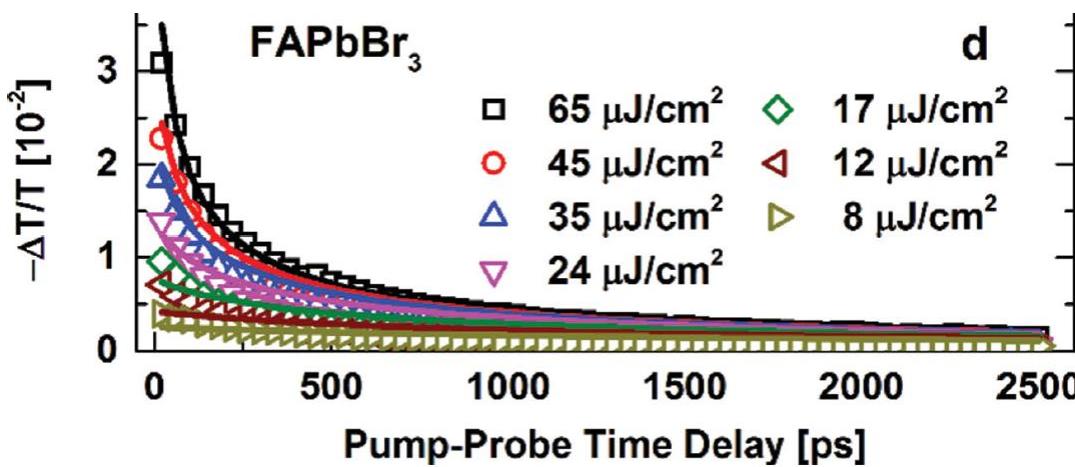
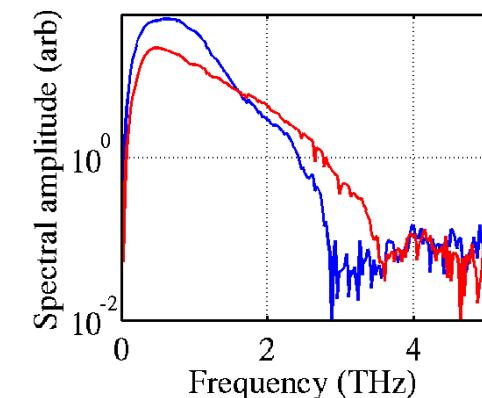
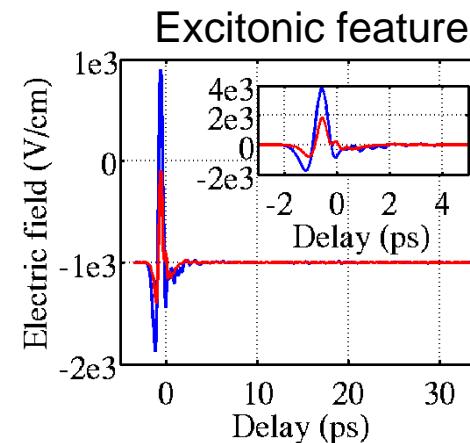
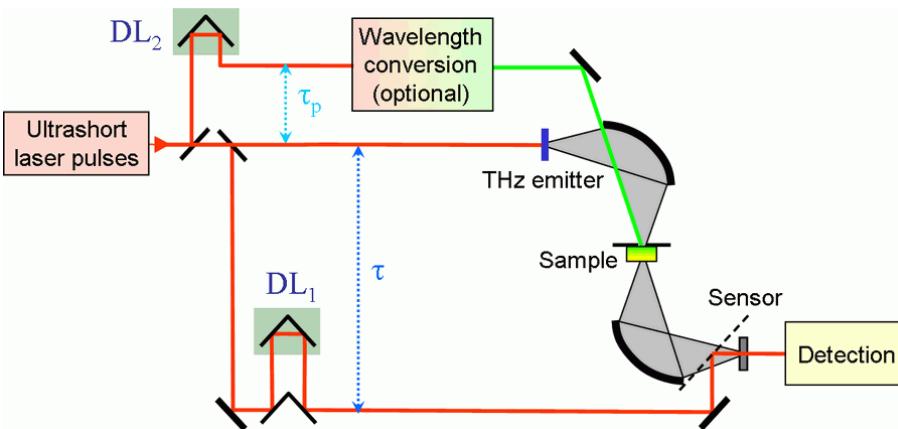


Lifetime:

$$\frac{dn}{dt} = G - E - R = -R_{\text{rad}} - R_{\text{non-rad}}$$

Sensitive to all carriers

- Optical pump THz-probe spectroscopy:

**d**

$$\frac{dn}{dt} = -k_3 n^3 - k_2 n^2 - k_1 n$$

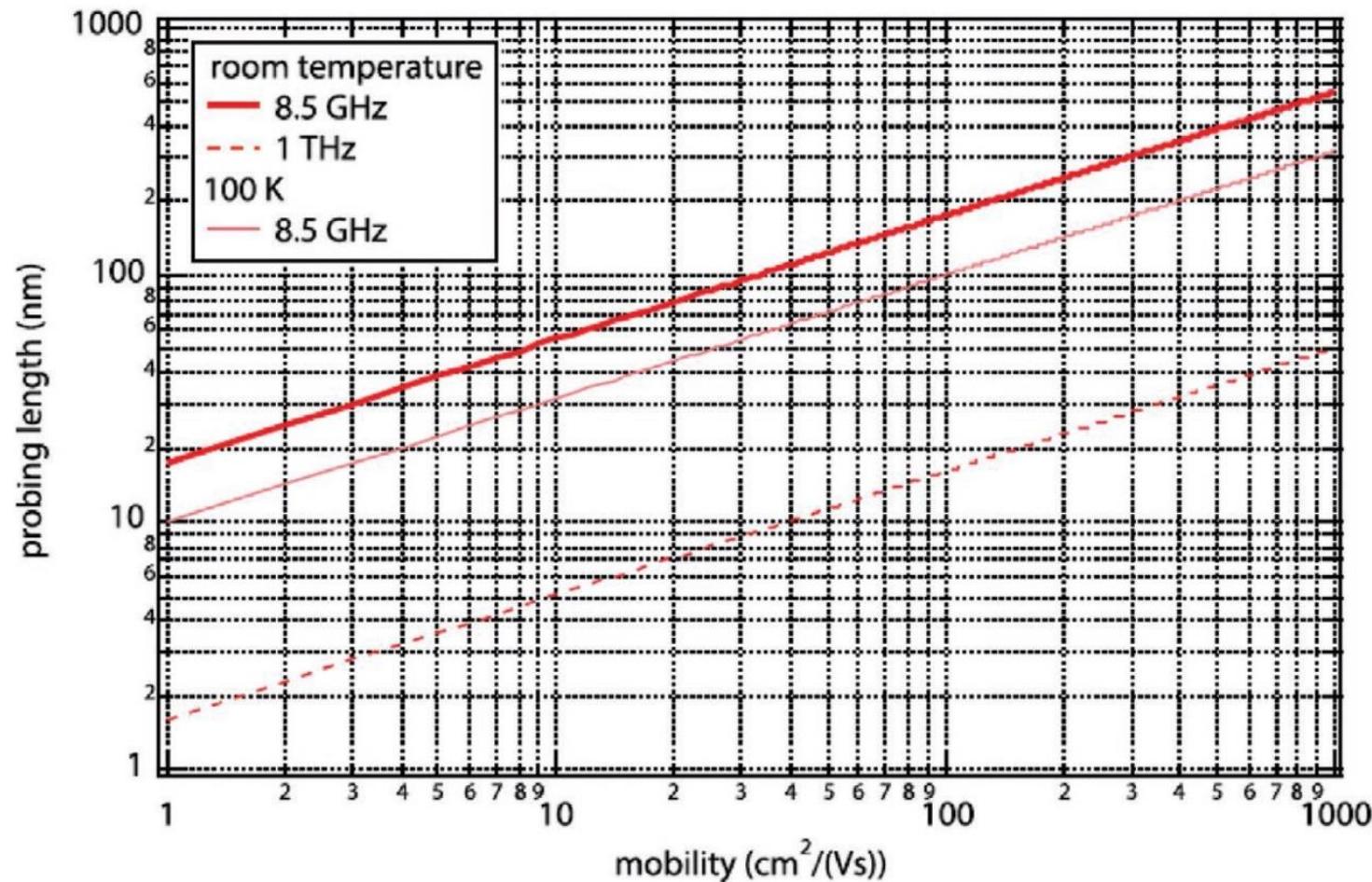
$$\Delta S = -\epsilon_0 c (n_a + n_b) \frac{\Delta T}{T}$$

$$\mu = \frac{\Delta S A_{eff}}{N e} \quad D = \frac{\mu k_B T}{e} \quad L_D(n) = \sqrt{\frac{D}{R_{total}(n)}}$$

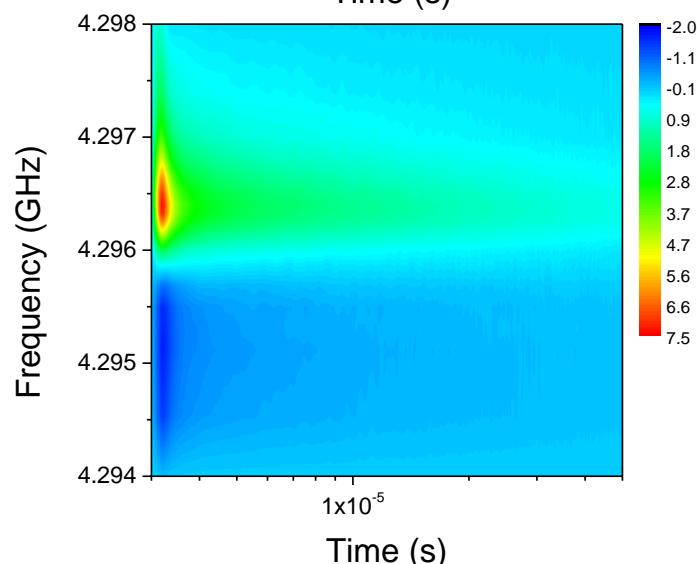
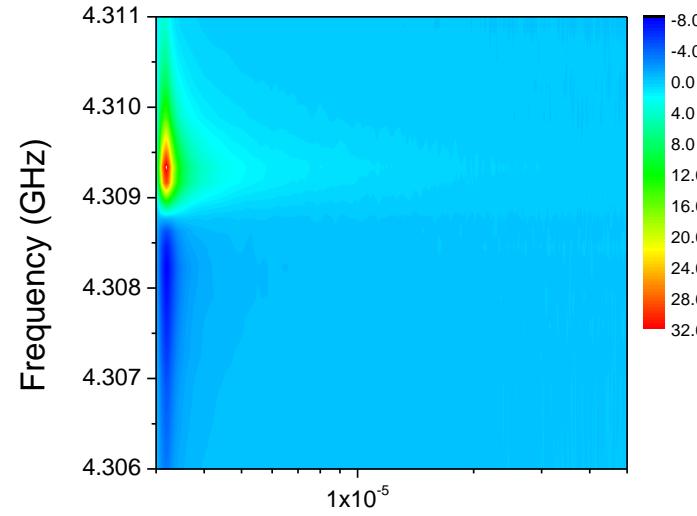
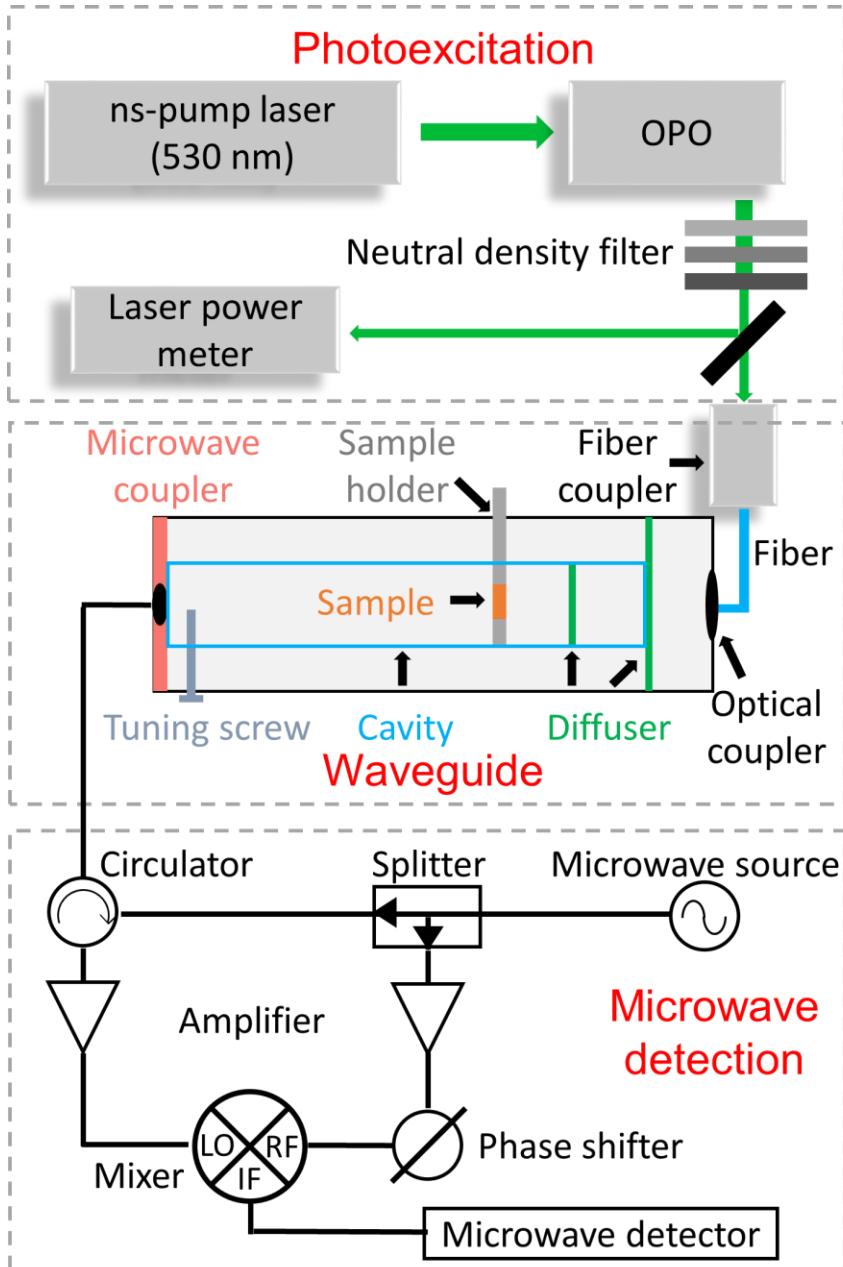
Lin Q. et al. *Adv. Funct. Mater.* 2017, 27(38): 1702485.

Rehman W. et al. *Adv. Mater.* 2015, 27(48): 7938-7944.

TRMC & OPTP

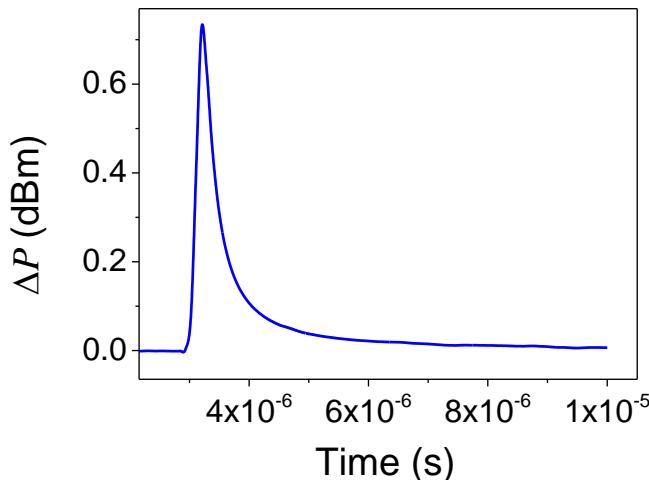


Background Characterization Application Summary

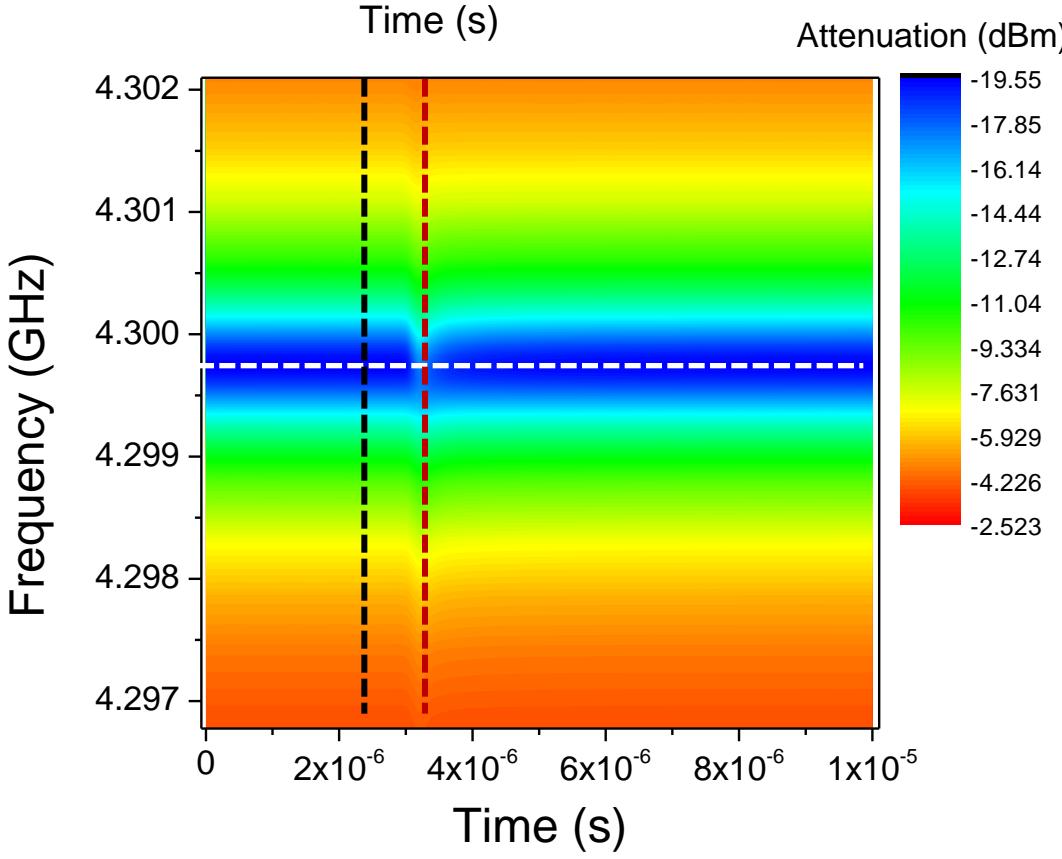
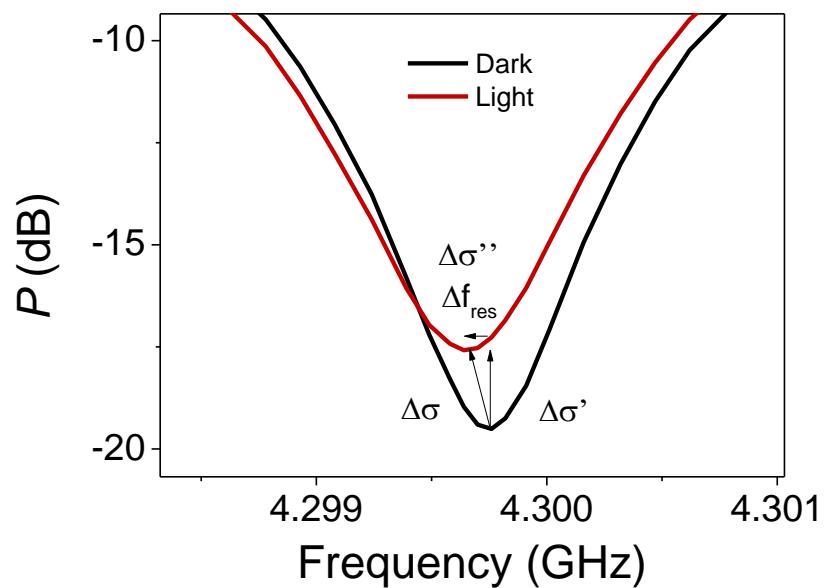


R.Li, Q. Lin* *et al.*, **J. Phys. Chem. Lett.**, 12: 1726-1733 (2021).
 F. Yao*, Q. Lin*, **ACS Photonics**, 12:2103652 (2022).
 Y. Li, Q. Lin*, **Appl. Phys. Rev.**, 10:011406 (2023).

1. TRMC dynamics



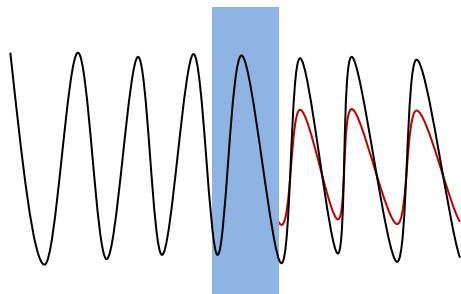
2. TRMC Spectra: (complex conductivity, phase information)



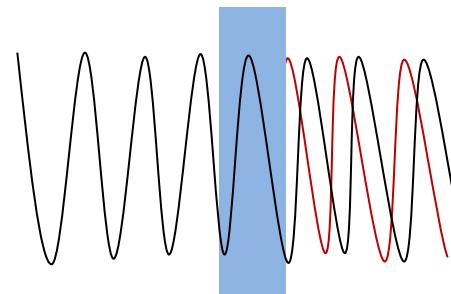
— Dark

— Light

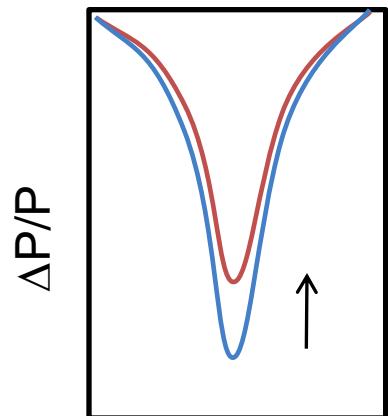
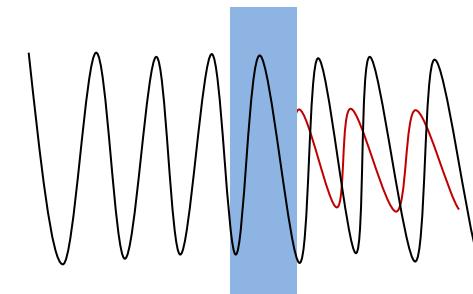
Photoconductive effect



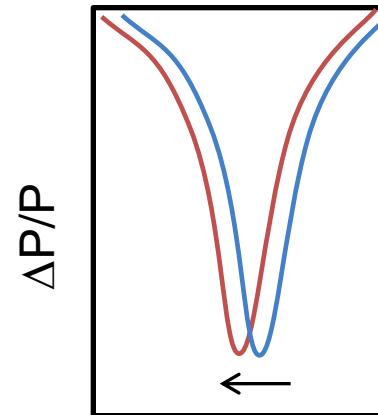
Photodielectric effect



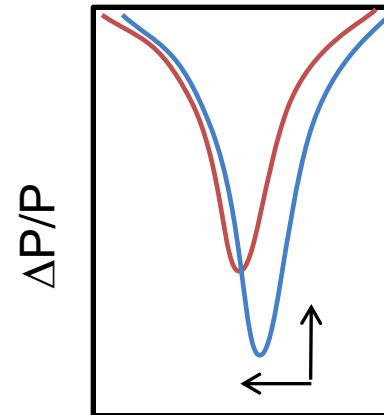
Mixed effect



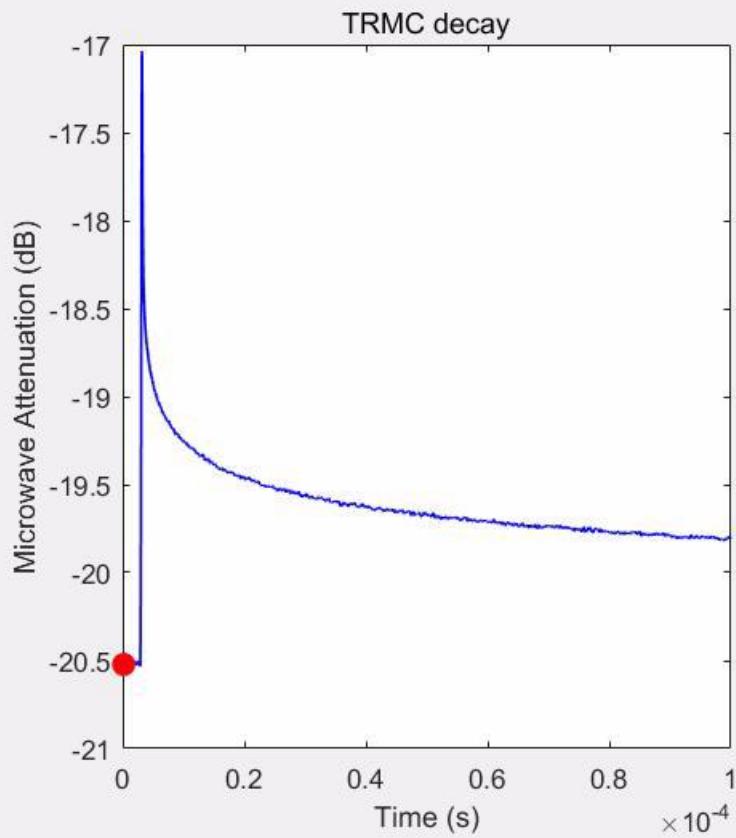
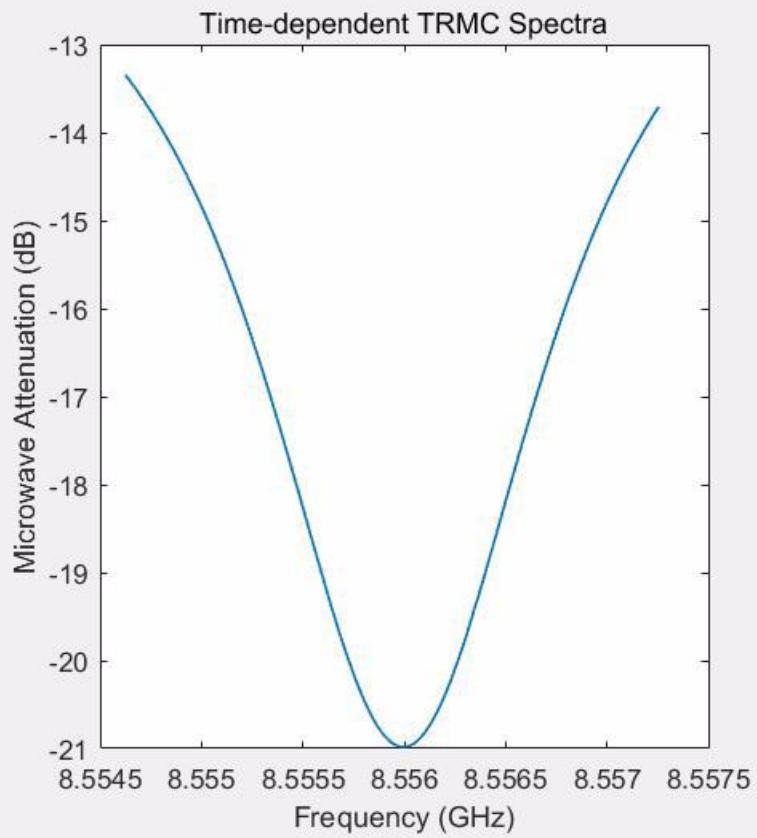
Frequency (GHz)

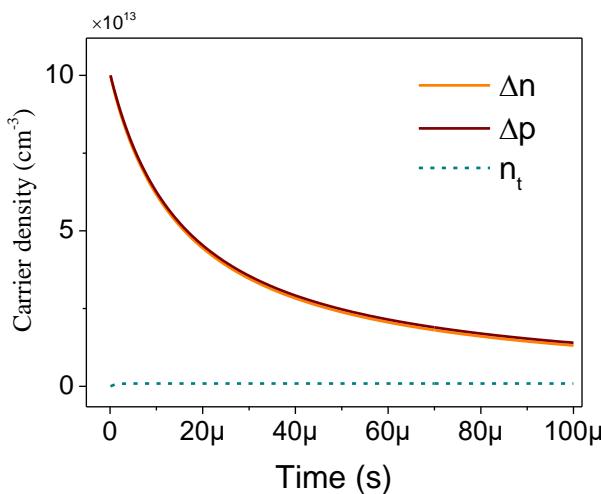
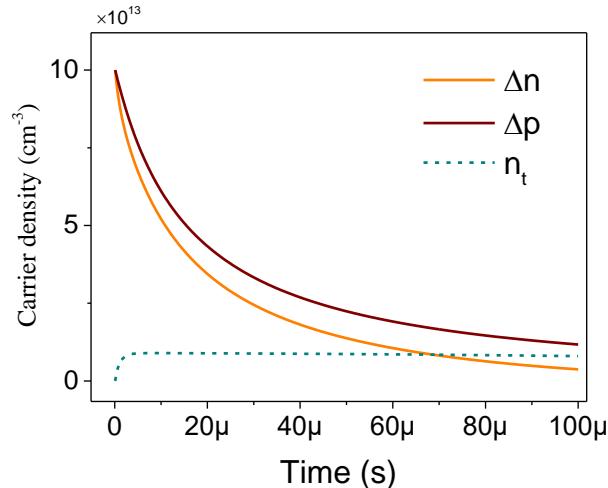
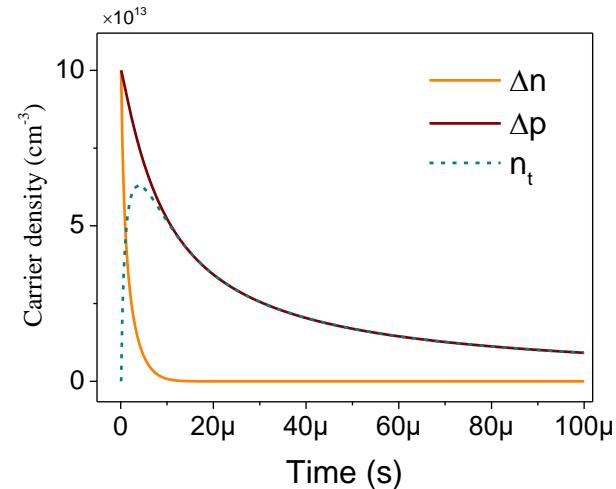


Frequency (GHz)



Frequency (GHz)



$N_t = 1e12 \text{ cm}^{-3}$  $N_t = 1e13 \text{ cm}^{-3}$  $N_t = 1e14 \text{ cm}^{-3}$ 

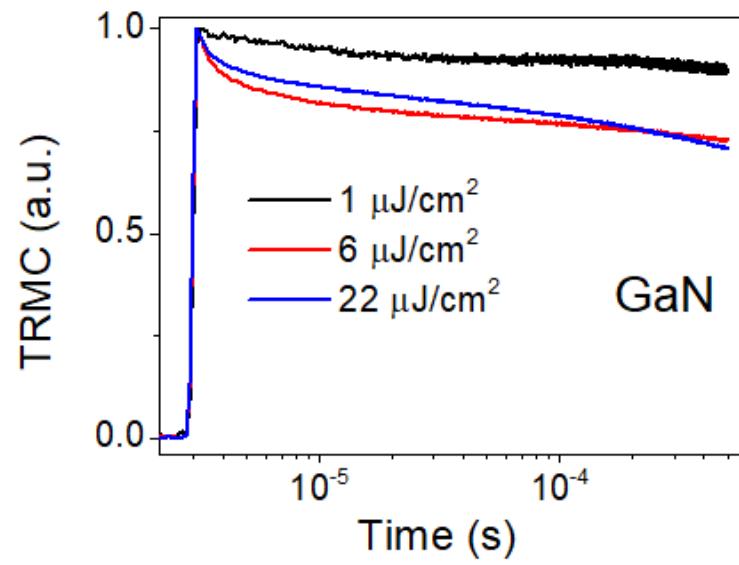
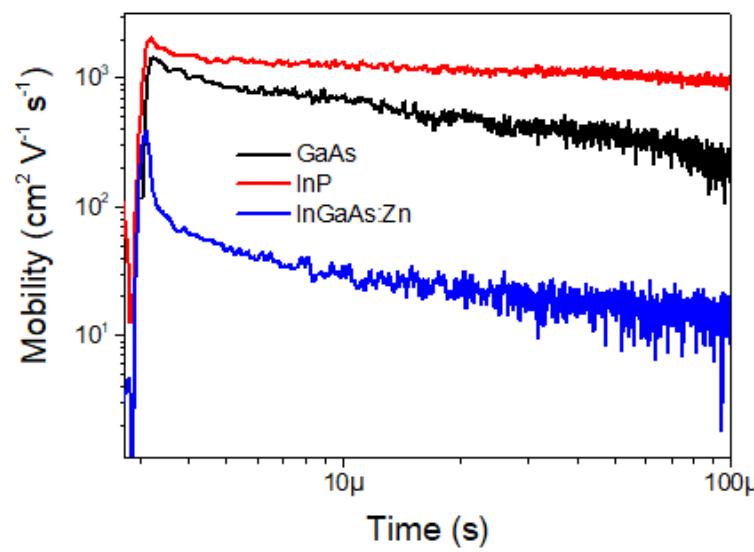
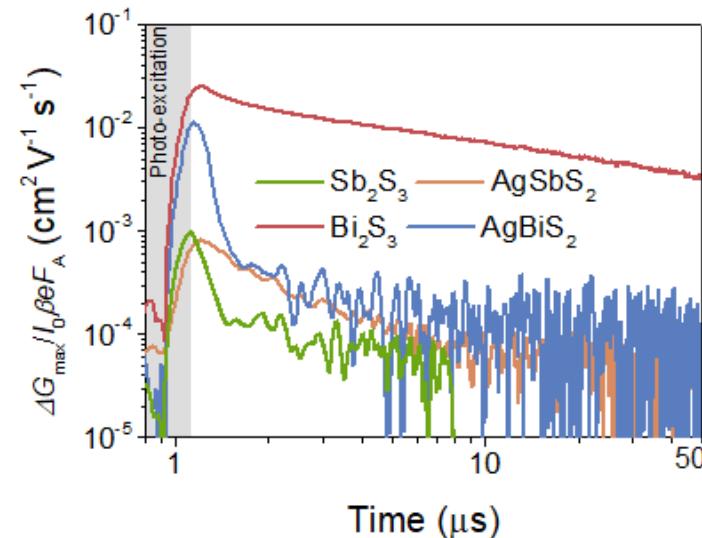
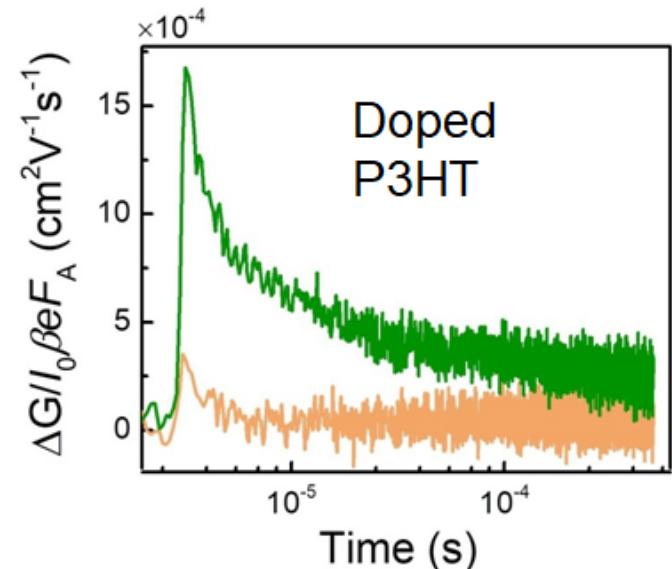
Continuous equation

$$\frac{d\Delta n}{dt} = G_c - k_2 \Delta n (\Delta p + p_0) - k_T \Delta n (N_T - n_t)$$

Density of trap state

$$\frac{d\Delta p}{dt} = G_c - k_2 \Delta n (\Delta p + p_0) - k_D n_t (\Delta p + p_0)$$

$$\frac{dn_t}{dt} = k_T \Delta n (N_T - n_t) - k_D n_t (\Delta p + p_0)$$

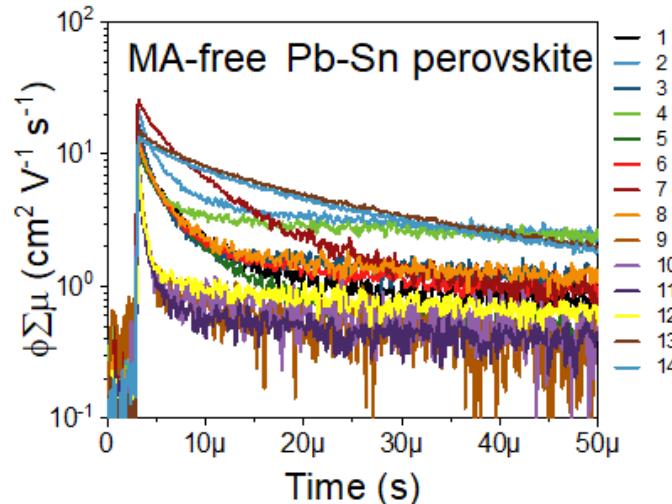
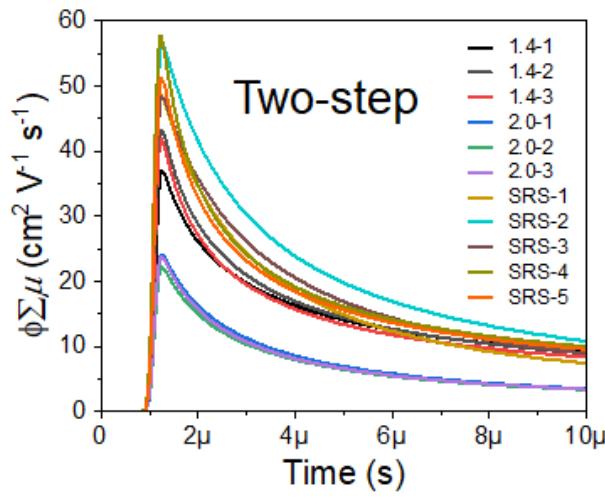
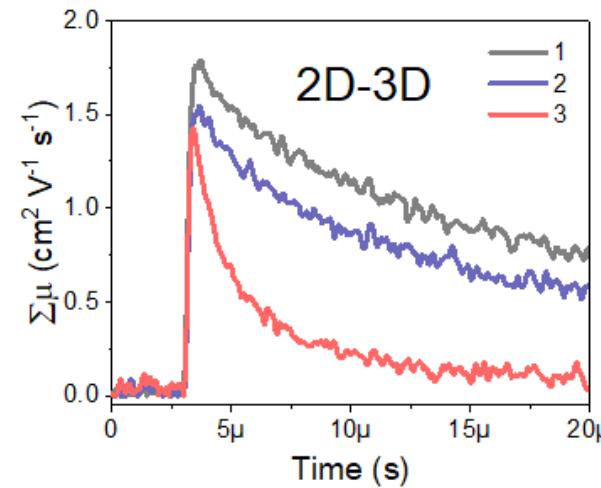
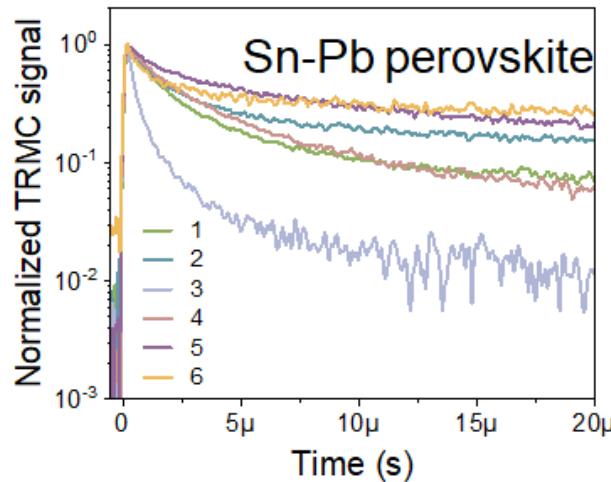


Q. Lin* *et al.*, **Nat. Commun.**, 2021, 12: 1531.

Q. Lin* *et al.*, **Appl. Phys. Rev.**, 2022, 9: 021405.

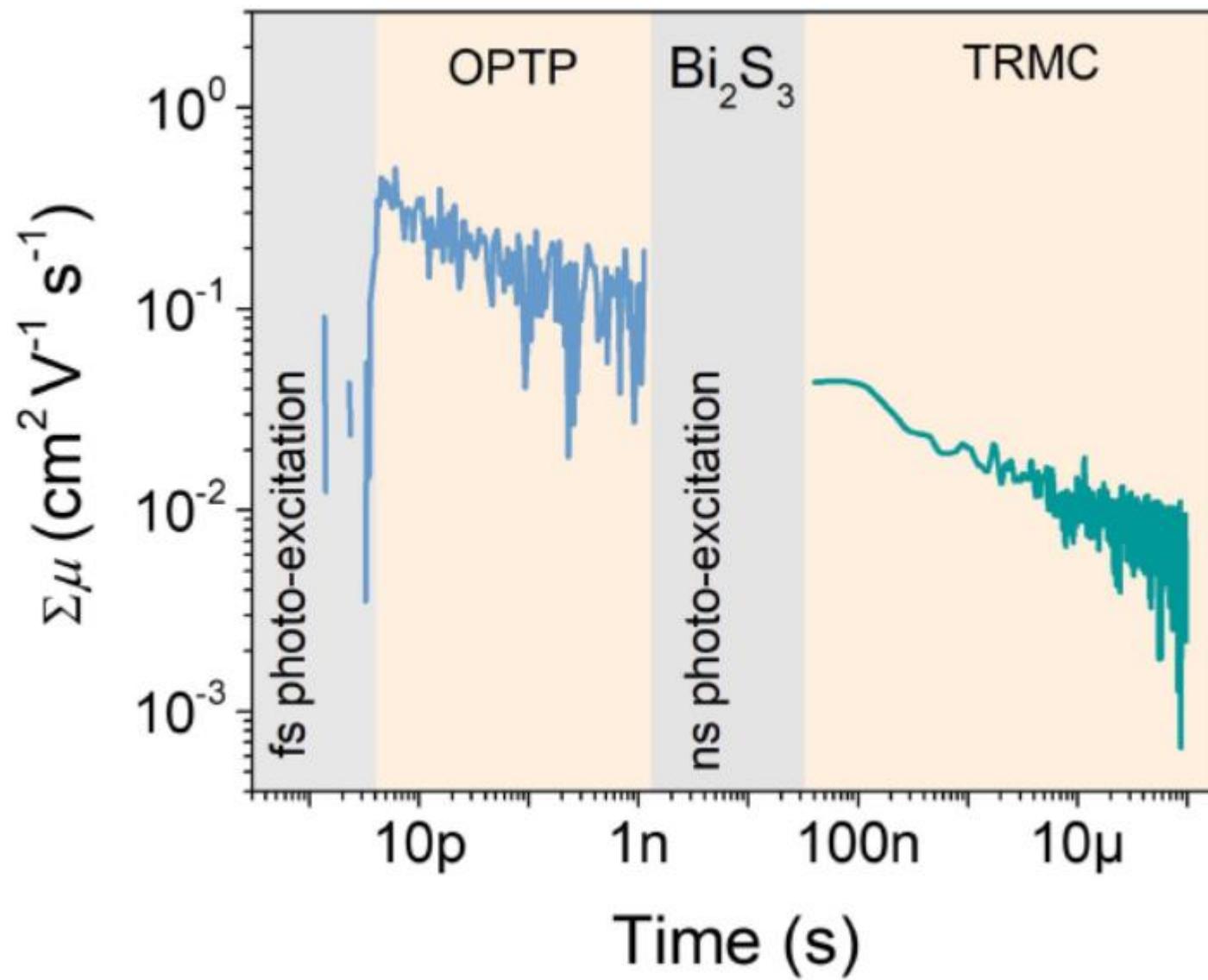
Q. Lin* *et al.*, **ACS Energy Lett.**, 2023, 8: 1485-1492.

Q. Lin* *et al.*, **Matter**, 2022, 5: 2251-2264.



Nature Energy, 2023, DOI:10.1038/s41560-023-01274-z.
Nature Energy, 2023, DOI:10.1038/s4156-023-01295-8.
Nature Energy, 2023, DOI:10.1038/s41560-023-01377-7.

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Energy & Environmental Science, 2023, DOI: 10.1039/D3EE00869J.

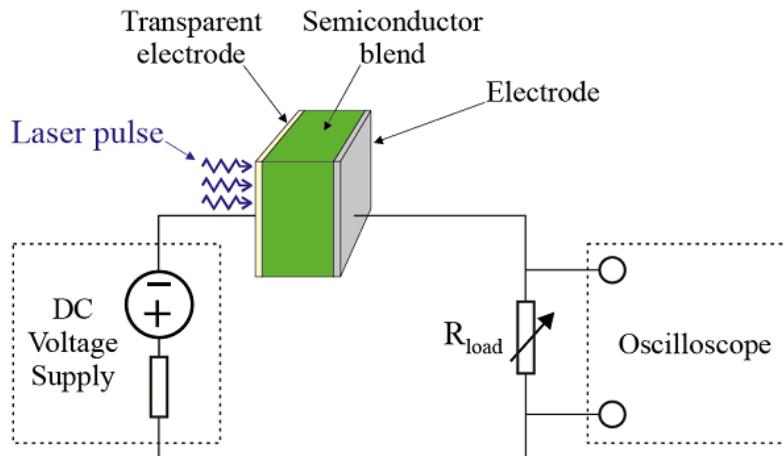


Electrical probe

Long-range charge transport could be **slowed down** by the grain boundaries and also electrode interfaces

Oscilloscopes can even not record the transients, if they are too fast (RC limited).

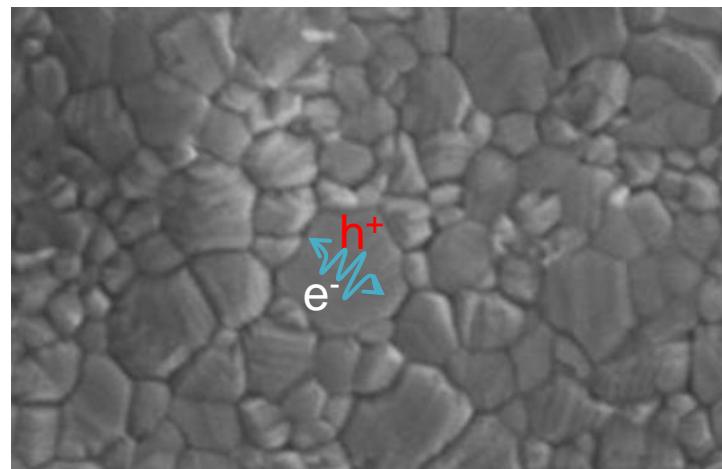
Used to **underestimate** the mobility

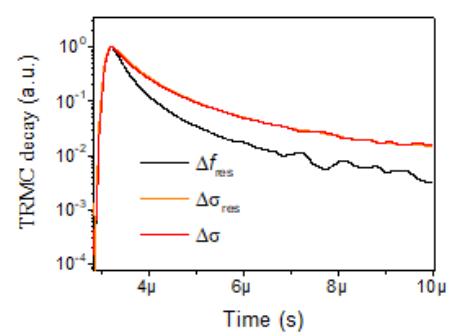
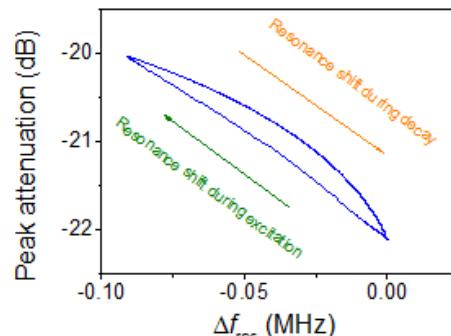
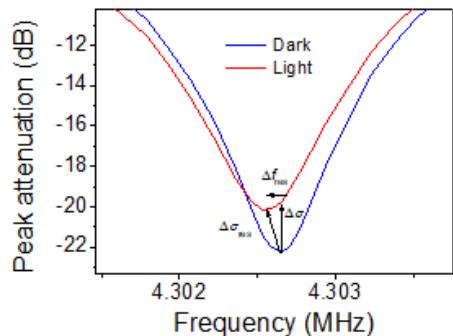
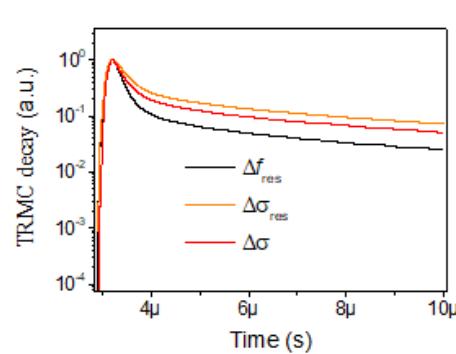
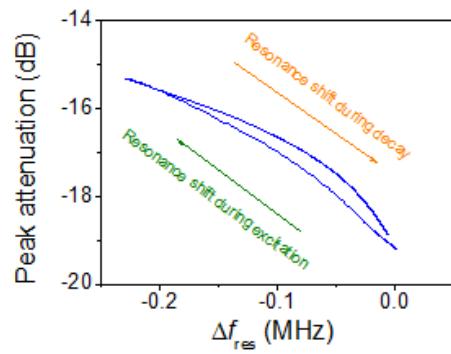
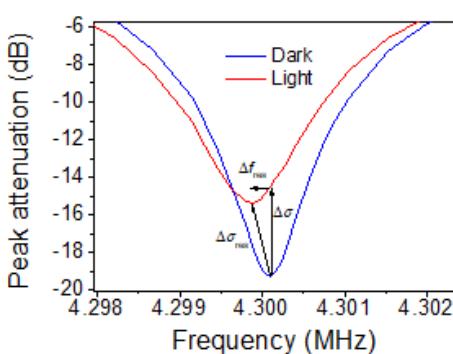
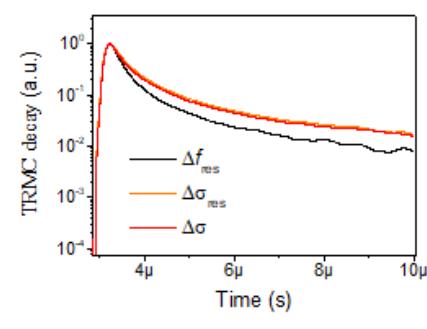
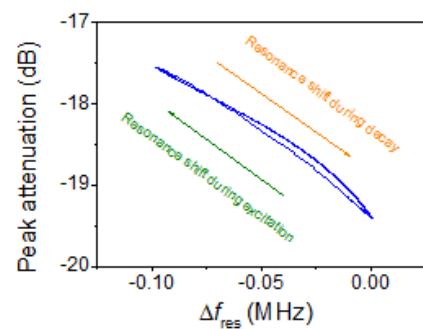
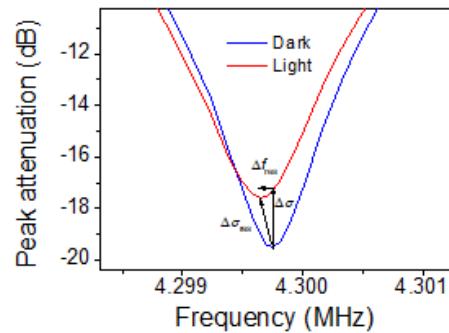


Optical probe

Short range within the crystals without the effect of grain boundaries

Used to **overestimate** the mobility

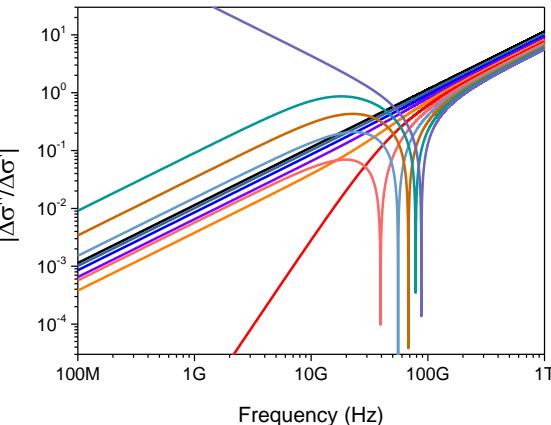
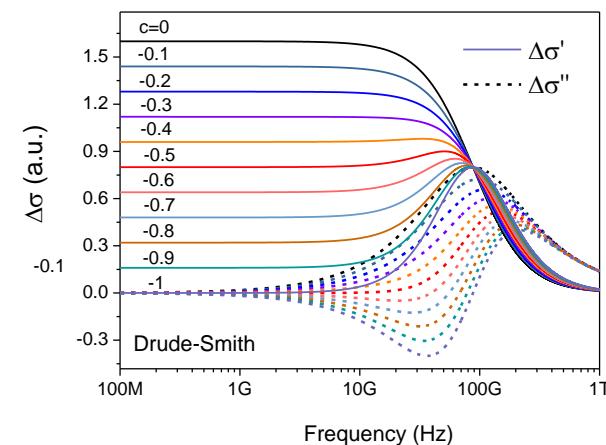


Perovskite 1**Perovskite 2****Perovskite 3**

Drude-Smith Model

$$\Delta\sigma_{DS}'(\omega) = \epsilon_0\omega_p^2 \frac{\tau}{1 + (\omega\tau)^2} \left[1 + c \frac{1 - (\omega\tau)^2}{1 + (\omega\tau)^2} \right]$$

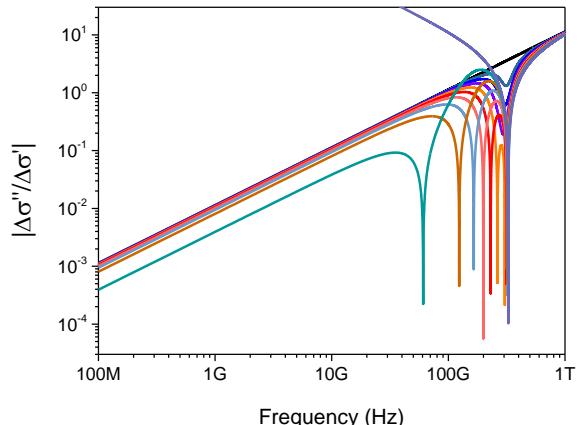
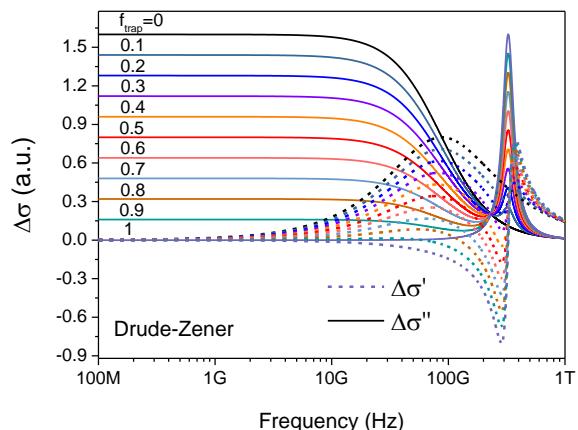
$$\Delta\sigma_{DS}''(\omega) = \epsilon_0\omega_p^2 \frac{\omega\tau^2}{1 + (\omega\tau)^2} \left[1 + \frac{2c}{1 + (\omega\tau)^2} \right]$$



Drude-Zener Model

$$\Delta\sigma_{DZ,trap}'(\omega) = \frac{\epsilon_0\omega_p^2\omega^2}{\tau} \frac{1}{(\omega_0^2 - \omega^2)^2 + \left(\frac{\omega}{\tau}\right)^2}$$

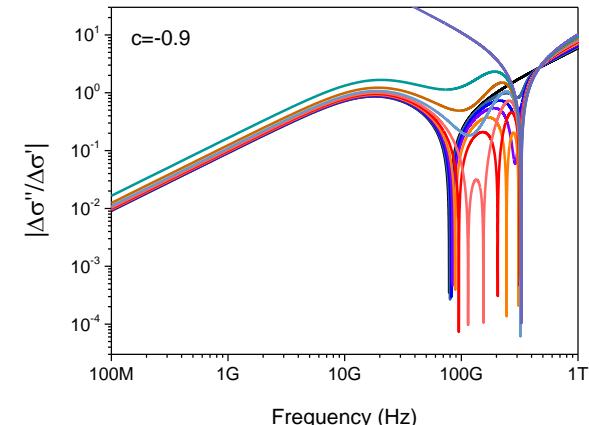
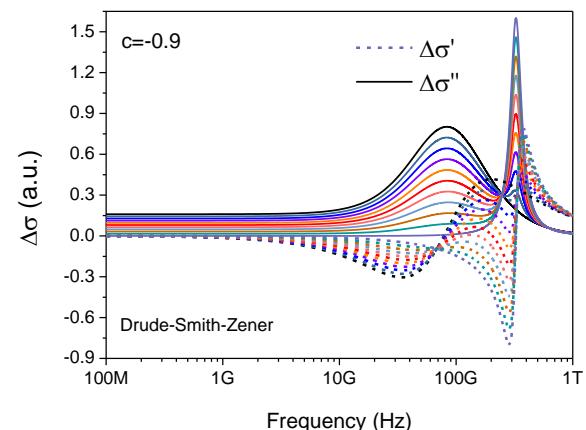
$$\Delta\sigma_{DZ,trap}''(\omega) = -\epsilon_0\omega_p^2\omega \frac{\omega_0^2 - \omega^2}{(\omega_0^2 - \omega^2)^2 + \left(\frac{\omega}{\tau}\right)^2}$$

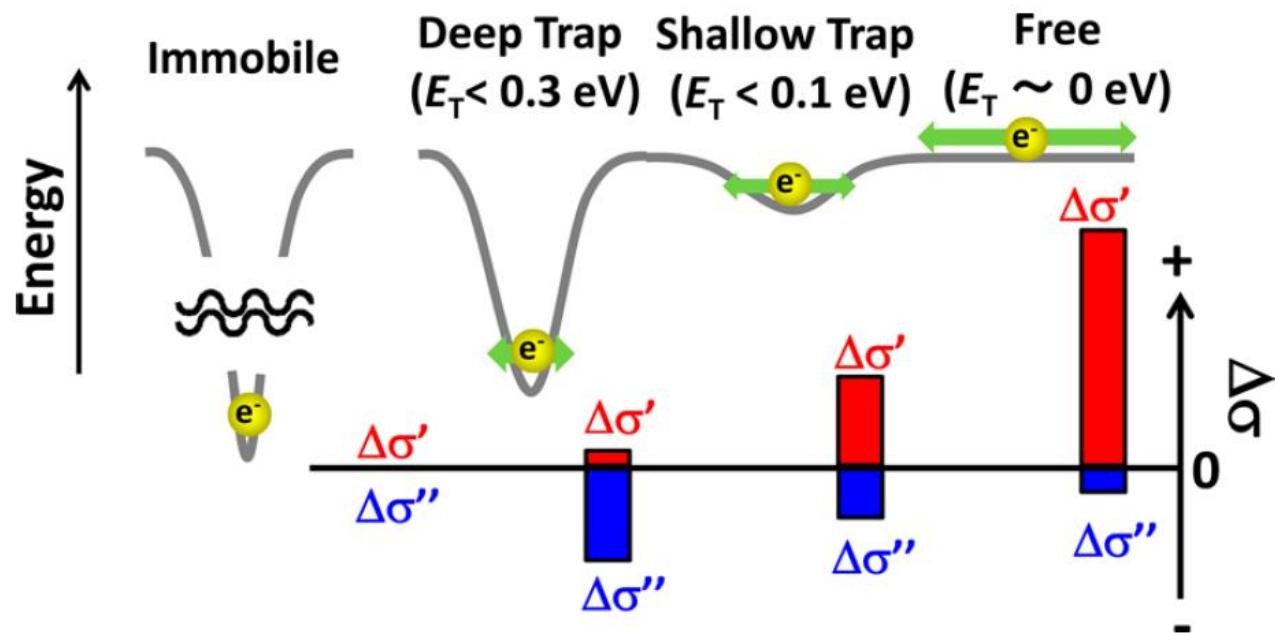


Mixed Model by Seki et al.

$$\Delta\sigma'(\omega) = (1 - f_{trap})\Delta\sigma_{DS}'(\omega) + f_{trap}\Delta\sigma_{DZ,trap}'(\omega)$$

$$\Delta\sigma''(\omega) = (1 - f_{trap})\Delta\sigma_{DS}''(\omega) + f_{trap}\Delta\sigma_{DZ,trap}''(\omega)$$





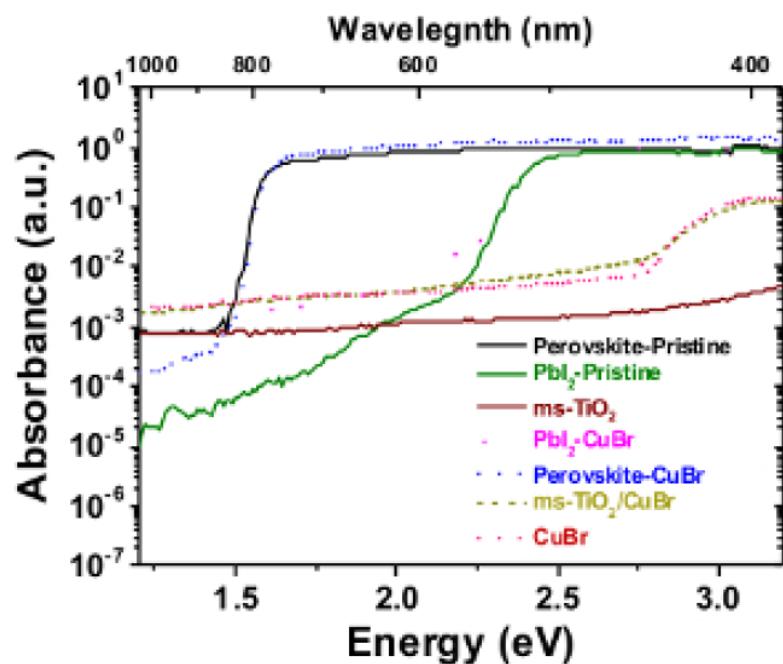
$$\omega_0^2 = \frac{2}{m^*} \frac{(4\pi\epsilon_0)^2}{e^4} E_T^3$$

Effective mass

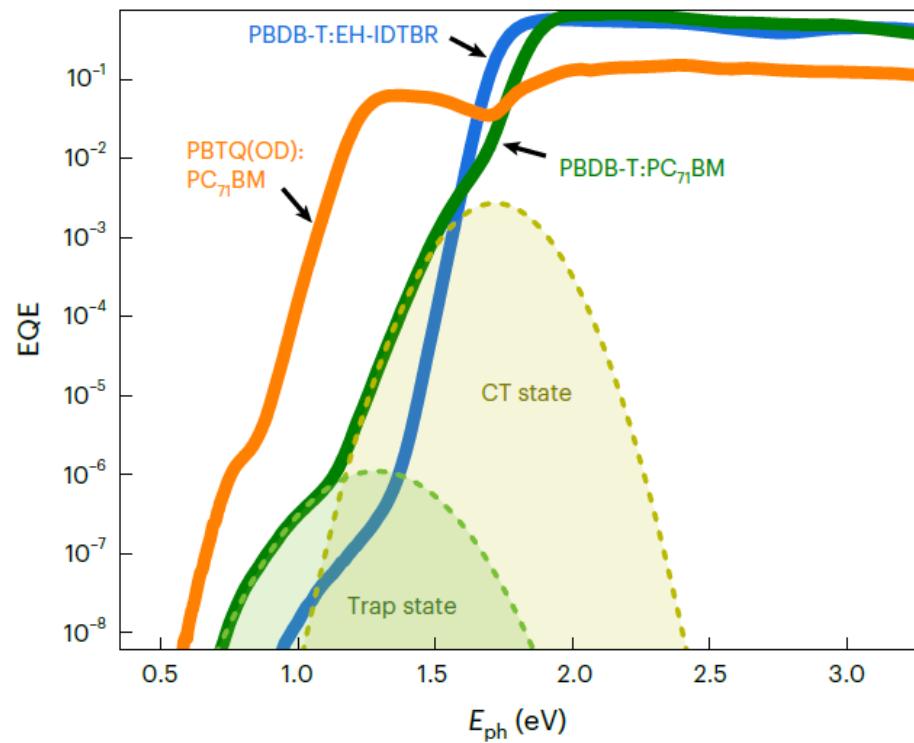
Energy level of trap states

Shallow trap states

Photothermal deflection spectroscopy (PDS)



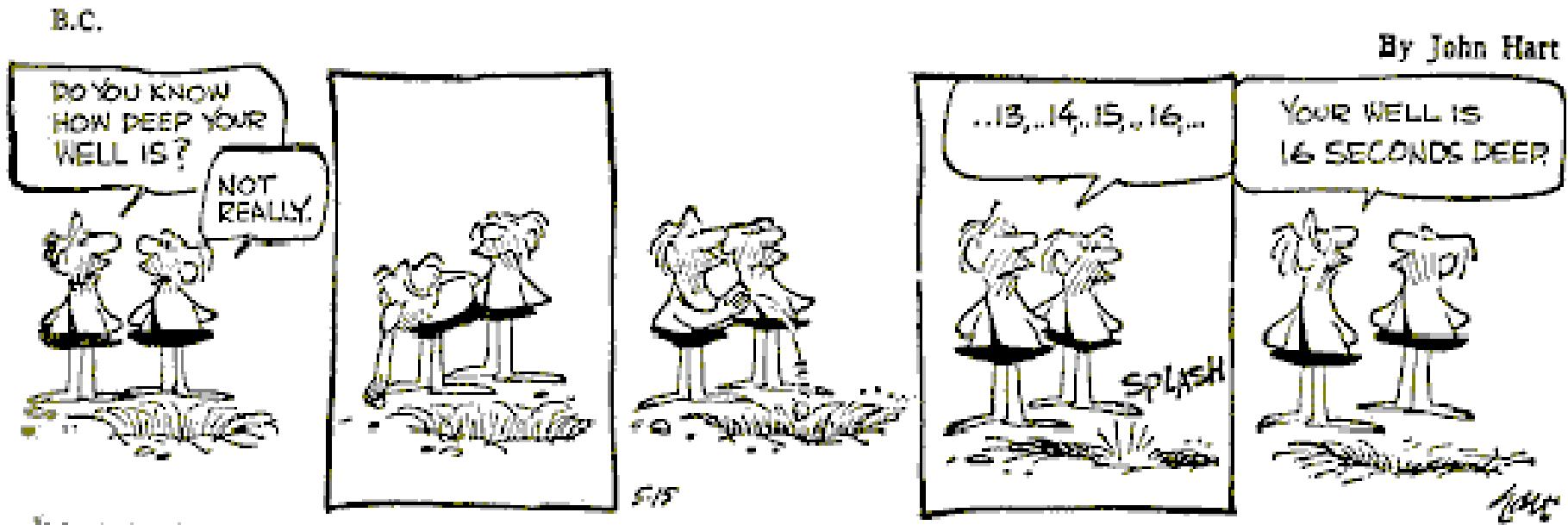
Sensitive-EQE



Abdi-Jalebi, M., et al., *Adv. Energy Mater.*
6: 1502472 (2016).

Oskar J. Sandberg, Ardalan Armin et al.,
Nat. Photonics. Doi.org/10.1038/s41566-023-01173-5 (2023).

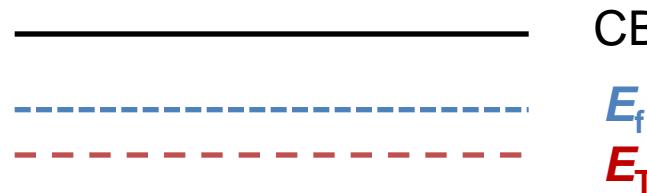
Pioneers in Measurements of Depth



By permission of John Hart and World Entertainment Inc.

Serway, Raymond A., Beichner, Robert J. and Jewett, John W. **Physics for Scientists and Engineers** 5th Edition, Saunders College Publishing: Orlandon, FL, 2000

Deep trap states (**n-type: $E_T < E_f$**)

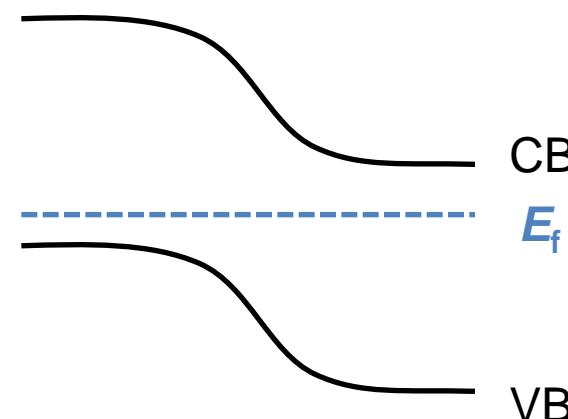
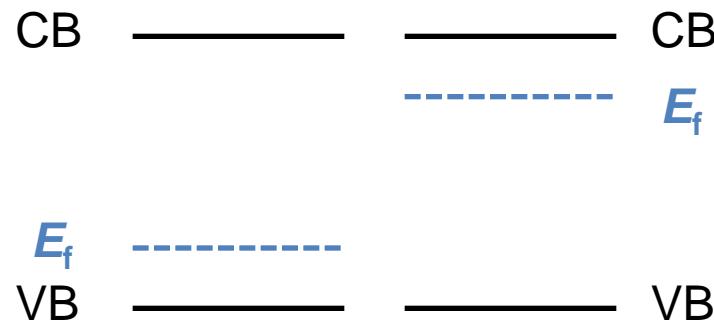


Junction capacitance

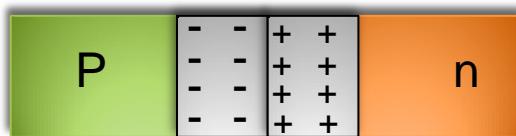
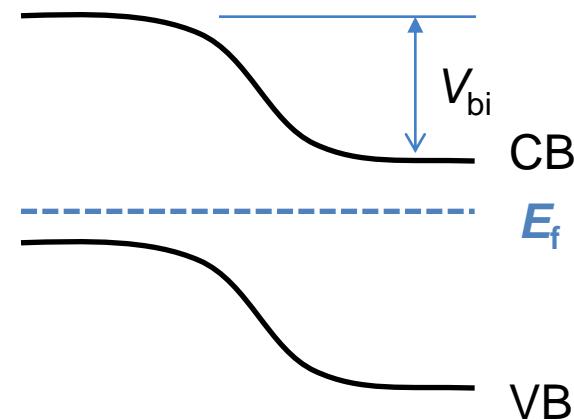
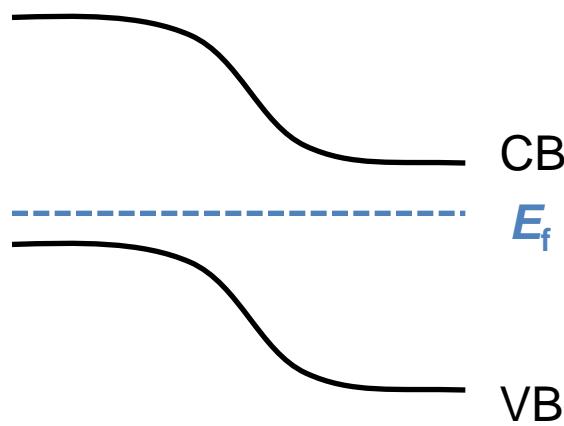
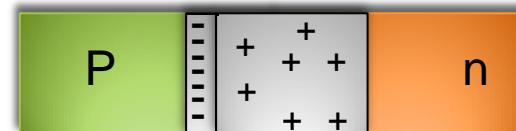
$$C = \frac{\epsilon A}{W}$$



Space charge region
(high resistance、 minor carriers)



Normal PN junction

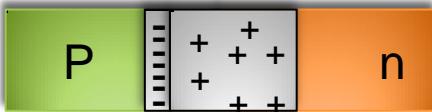
P+N junction (**W** of p-region is very narrow)

$$W = \sqrt{\frac{2\epsilon(V_{bi} + V)}{qn}}$$

Depletion width:
The higher concentration,
the narrower depletion width.

- C-V measurement

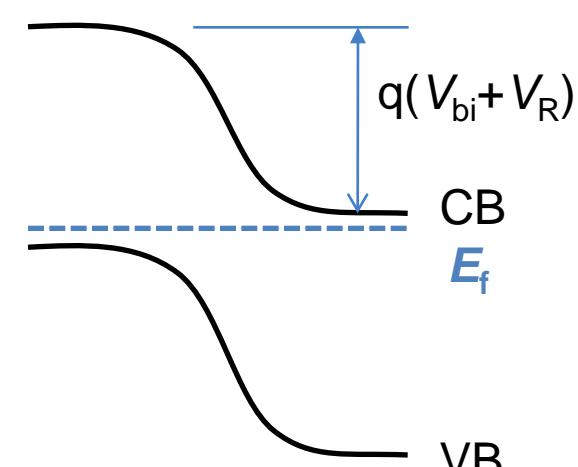
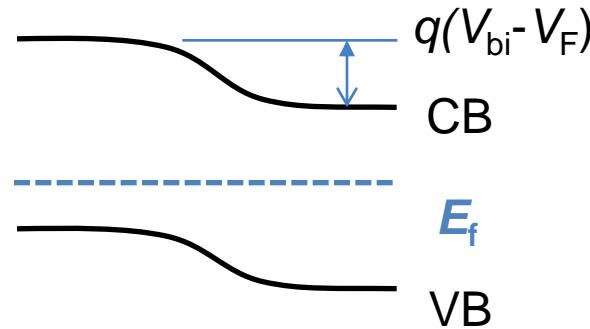
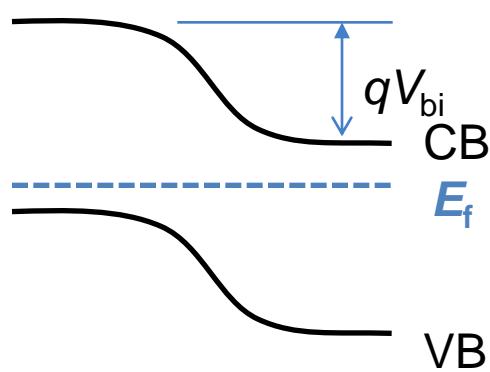
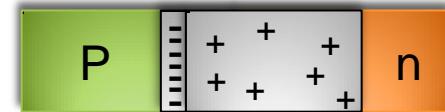
Equilibrium
P+N junction



Forward Bias
P+N junction



Reverse Bias
P+N junction



$$C = \frac{\epsilon A}{W}$$

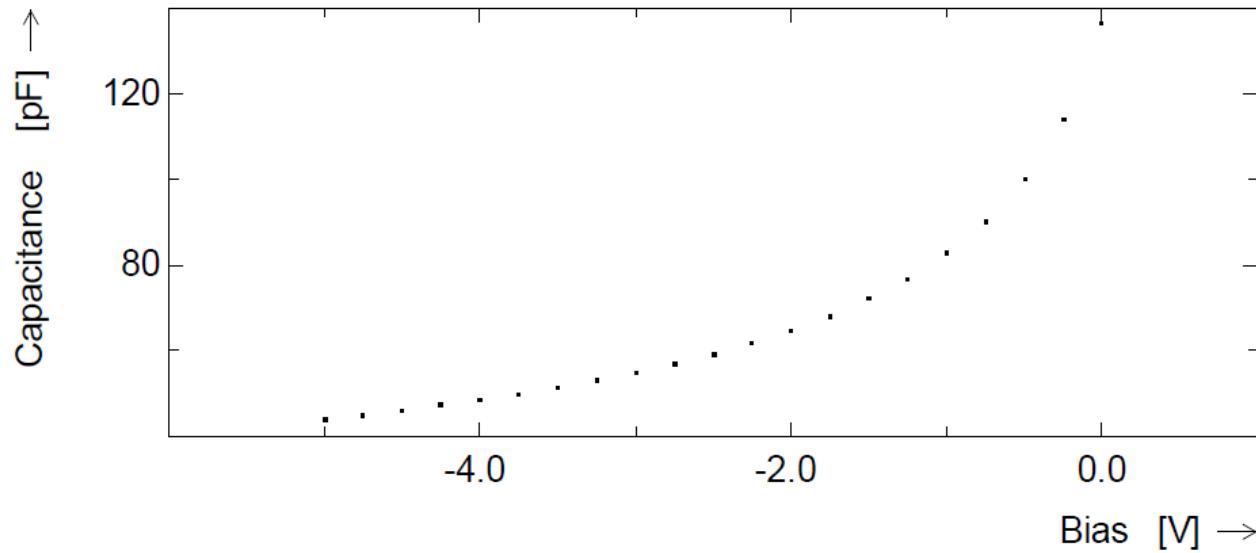
$$W = \sqrt{\frac{2\epsilon(V_{bi}+V)}{qn}}$$

$$C = A \sqrt{\frac{\epsilon q n}{2(V_{bi}+V)}}$$

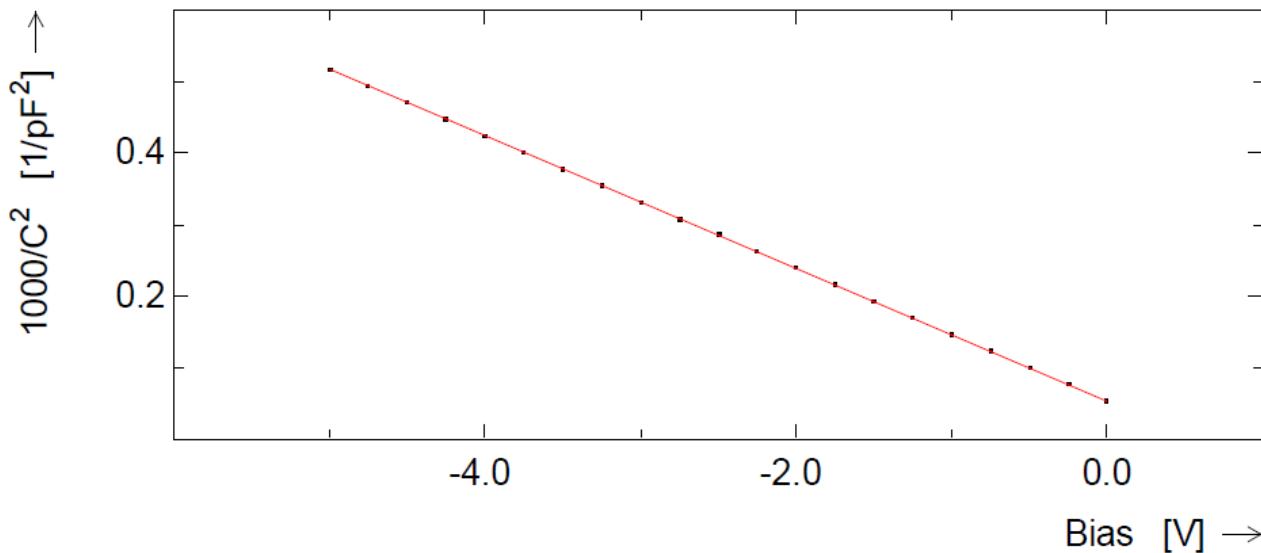
$$\frac{1}{C^2} = \frac{2}{A^2 \epsilon q n} (V_{bi} + V)$$

$$E_c - E_F = k_B T \ln\left(\frac{N_c}{n}\right)$$

$$q\varphi_B = qV_{bi} + (E_c - E_F)$$

Background**Characterization****Application****Summary**

Name = @A_001.KCA
Comm = Standard
ID = TestID
rclD = 1001
Date = 2010-07-29
Type = n-Si
Area = 8.00E-03 cm²
Temp = 270.15 K
N_S = 2.00E+15 cm⁻³
U_D = -0.581 V
phi_B = 0.800 eV
Correl = 1.00000



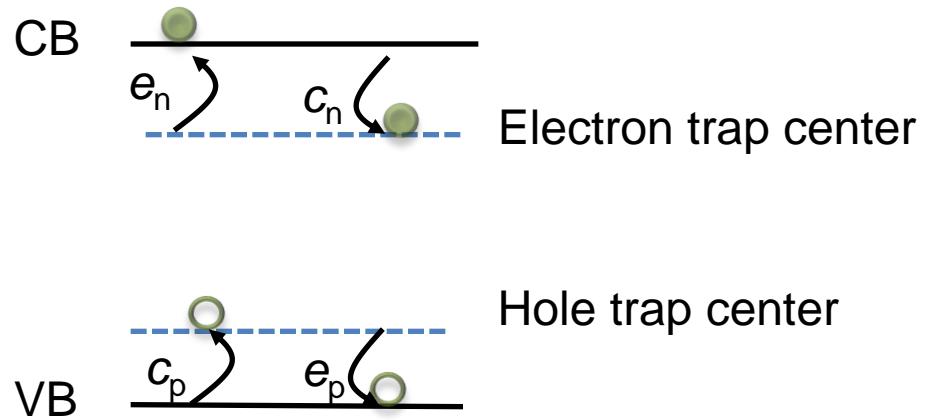
There are traps within the space charge region!

Thermal (electron) emission rate:

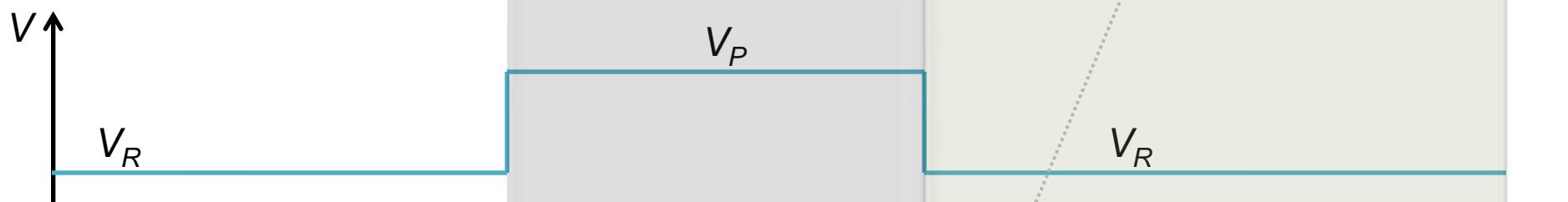
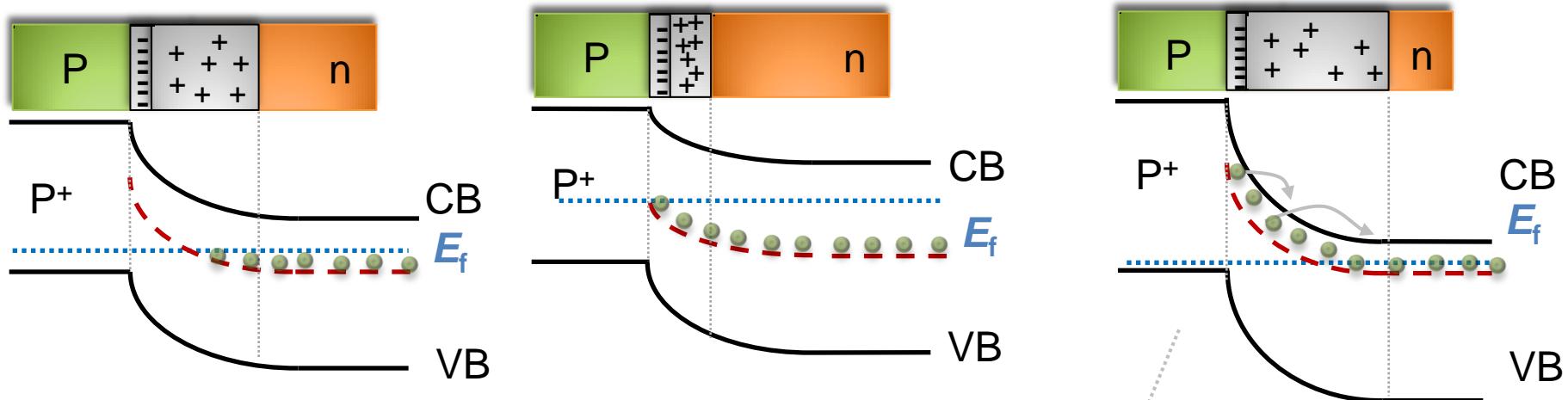
$$e_n = \frac{\sigma_n v_n N_c}{g} \exp\left(\frac{-(E_C - E_t)}{kT}\right)$$

$$v_n \propto T^{\frac{1}{2}} \quad N_c \propto T^{\frac{3}{2}}$$

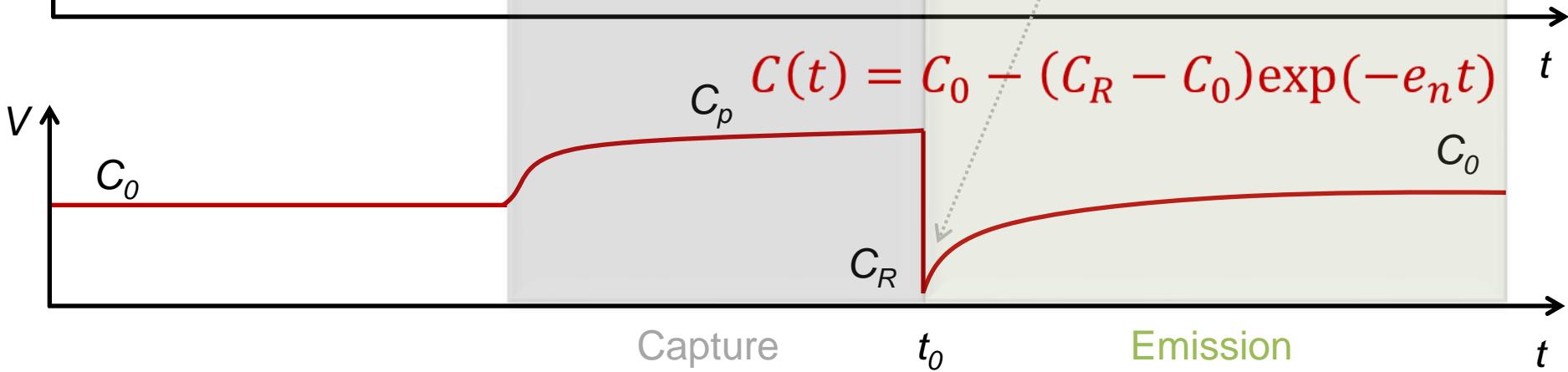
$$e_n = \sigma_n \beta T^2 \exp\left(-\frac{E_C - E_t}{kT}\right)$$



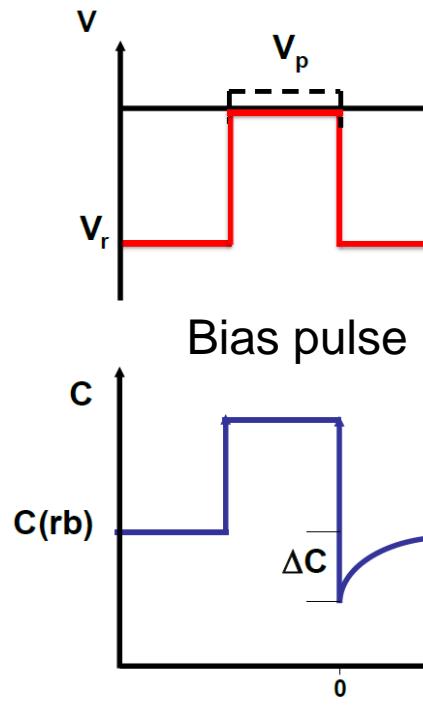
Transient capacitance



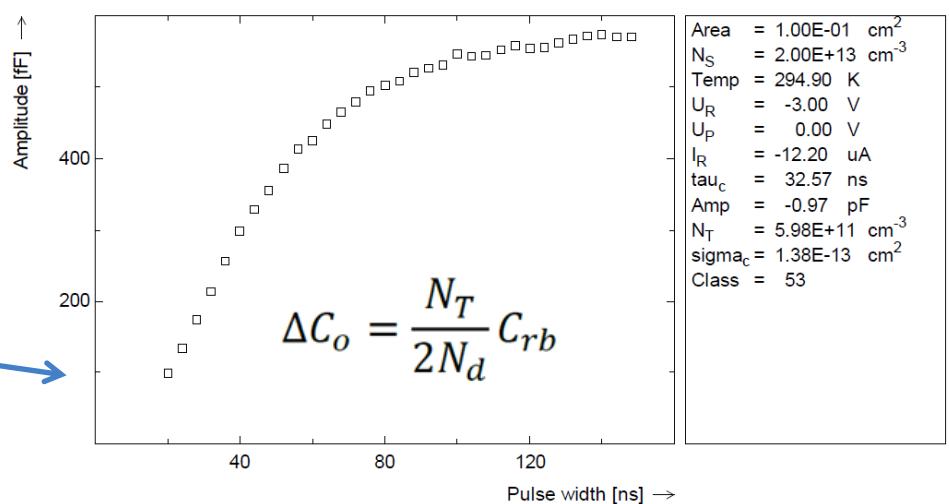
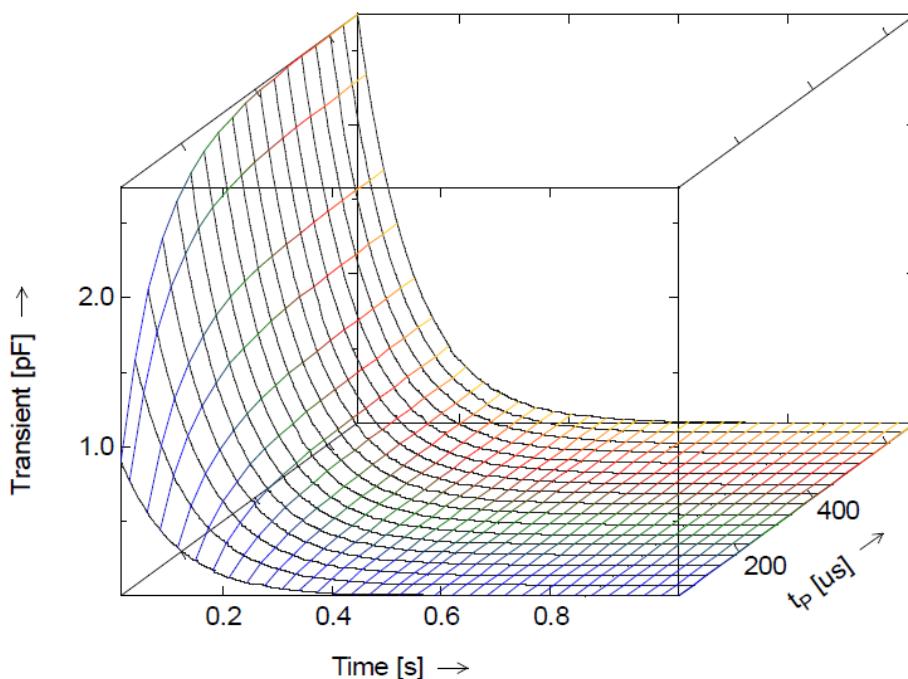
$$C(t) = C_0 - (C_R - C_0)\exp(-e_n t)$$



Optical pulse can also inject carriers within the SCR



Trap concentration can be obtained from the maximum amplitude of the DLTS transient



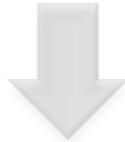
- Principle of DLTS

Thermal (electron) emission rate:

$$e_n = \frac{\sigma_n v_n N_c}{g} \exp\left(-\frac{(E_C - E_t)}{kT}\right)$$

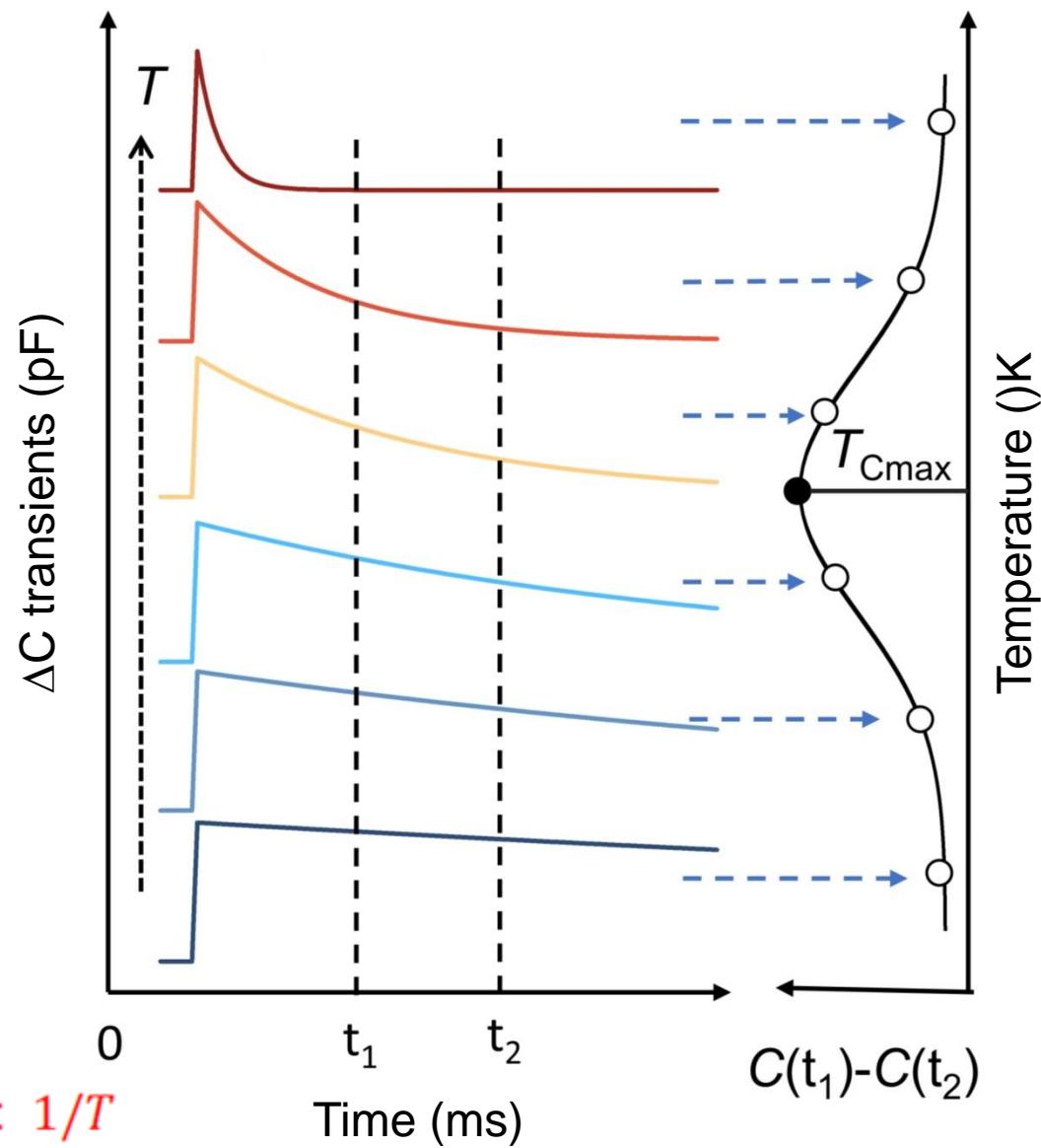
$$v_n \propto T^{\frac{1}{2}} \quad N_c \propto T^{\frac{3}{2}}$$

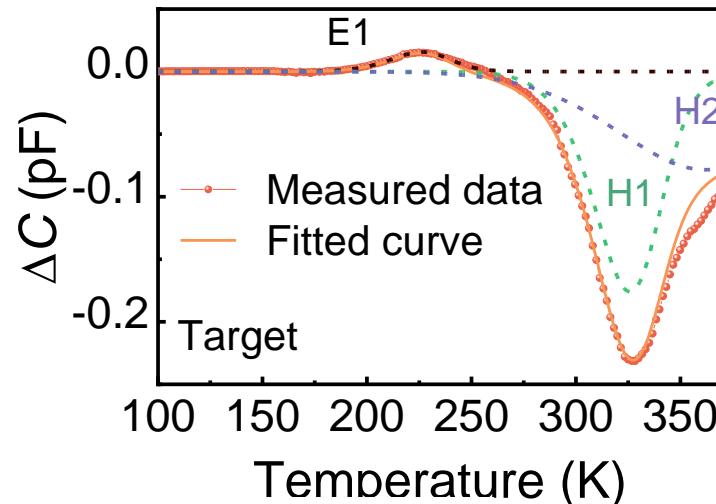
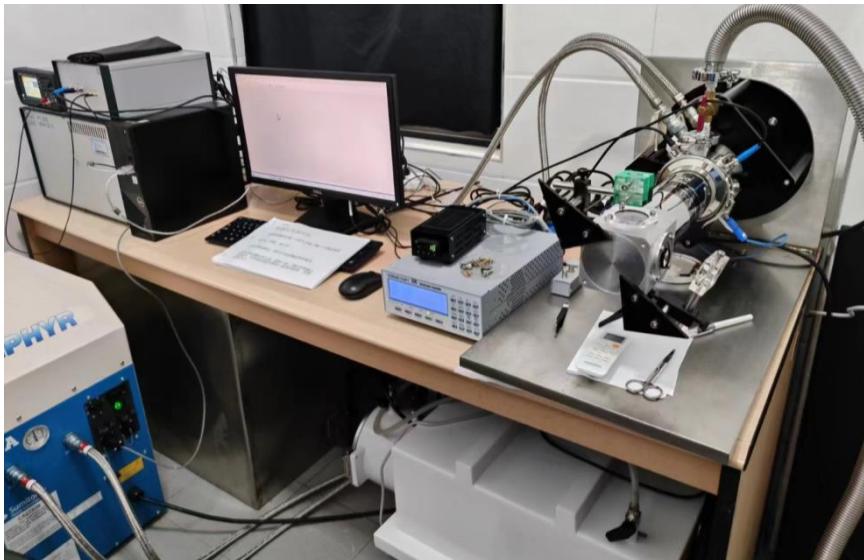
$$e_n = \sigma_n \beta T^2 \exp\left(-\frac{E_C - E_t}{kT}\right)$$



$$\ln \left[\frac{e_n}{T^2} \right] = \ln (\beta \sigma_n) - \frac{E_c - E_T}{kT}$$

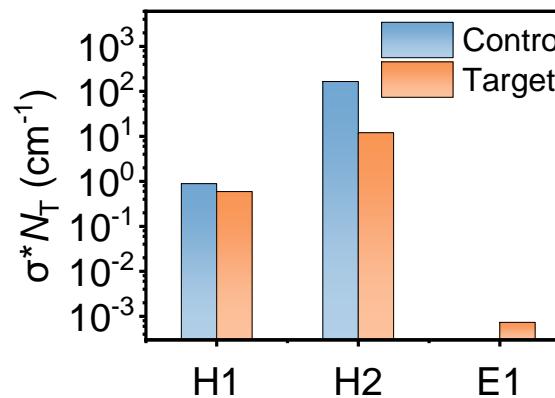
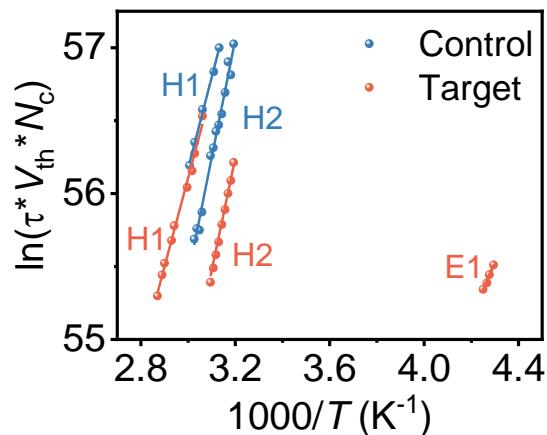
Arrhenius plot of $\ln \left[\frac{e_n}{T^2} \right]$ against $1/T$





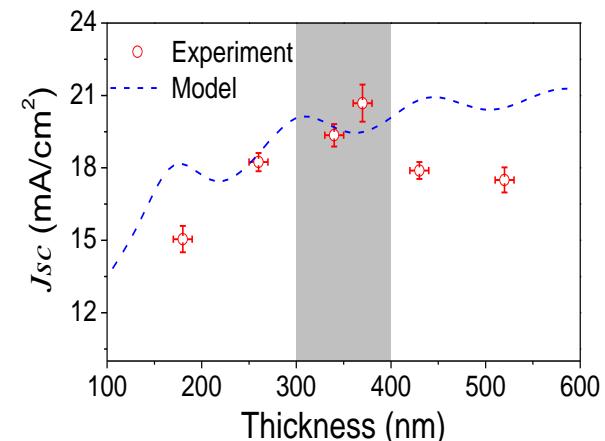
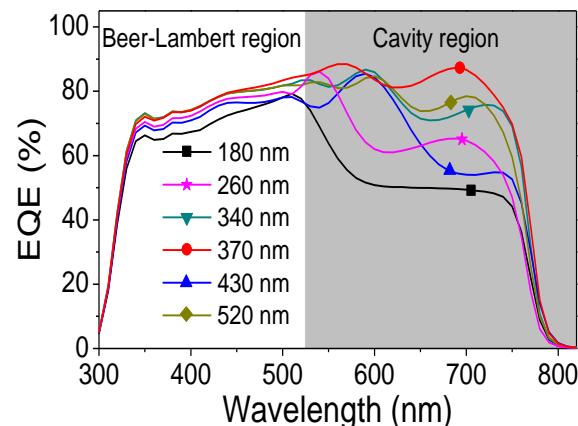
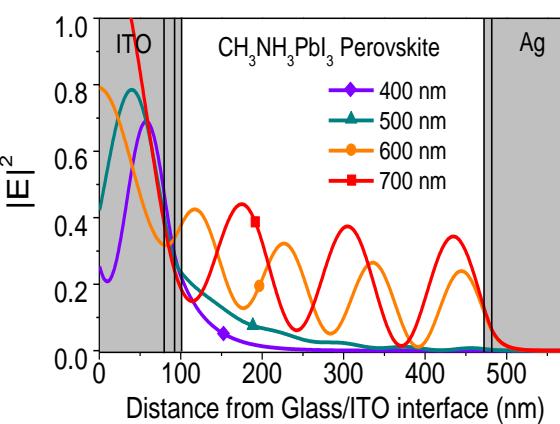
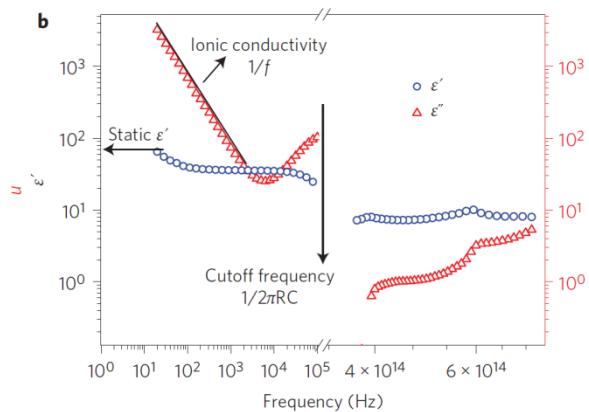
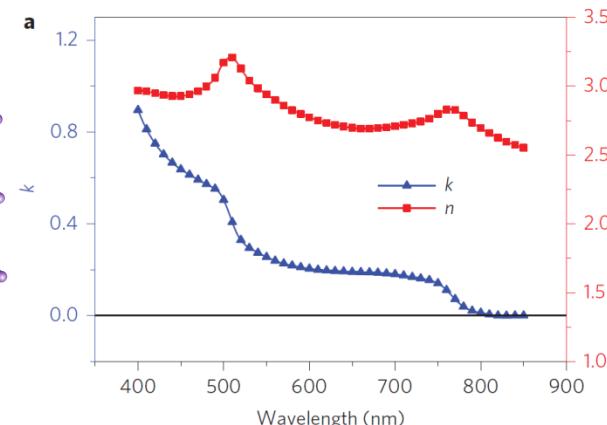
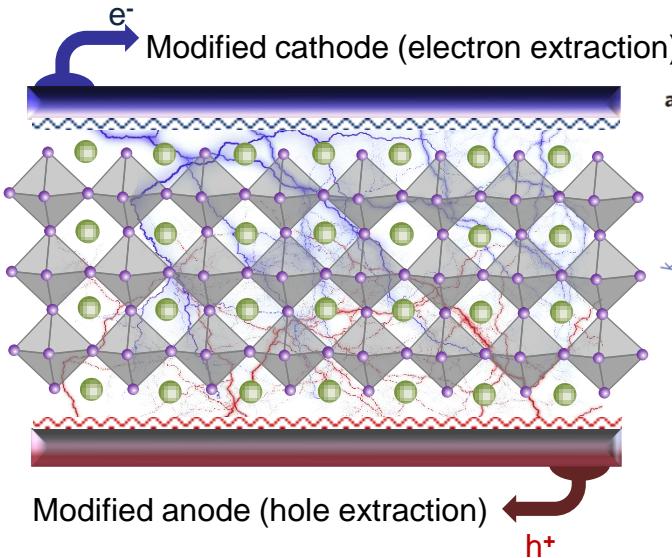
Arrhenius plot of $\ln \left[\frac{e_n}{T^2} \right]$ against $1/T$

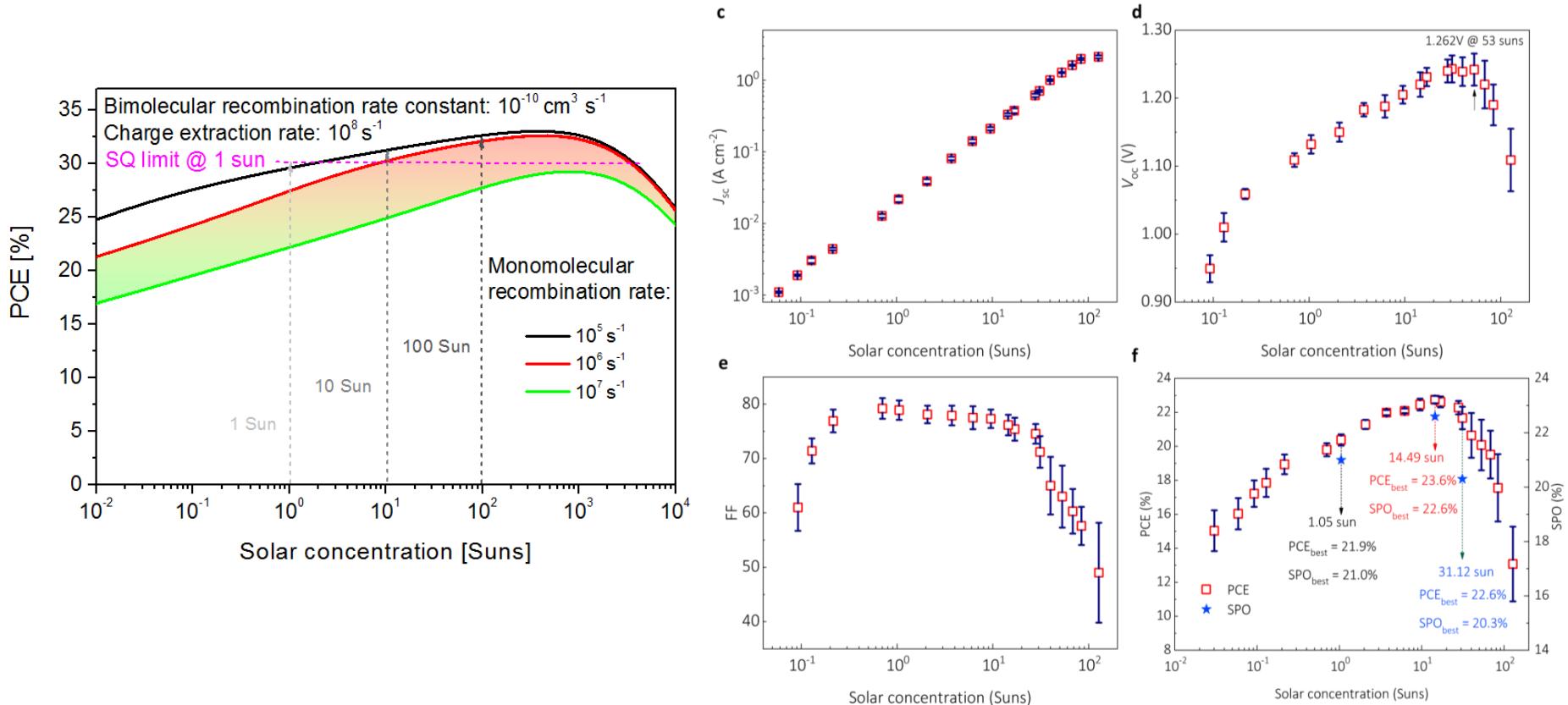
$$\ln \left[\frac{e_n}{T^2} \right] = \ln (\beta \sigma_n) - \frac{E_c - E_T}{kT}$$



➤ Perovskite solar cells: strategies to boost the PCE

1. Optical cavity optimization → J_{sc}

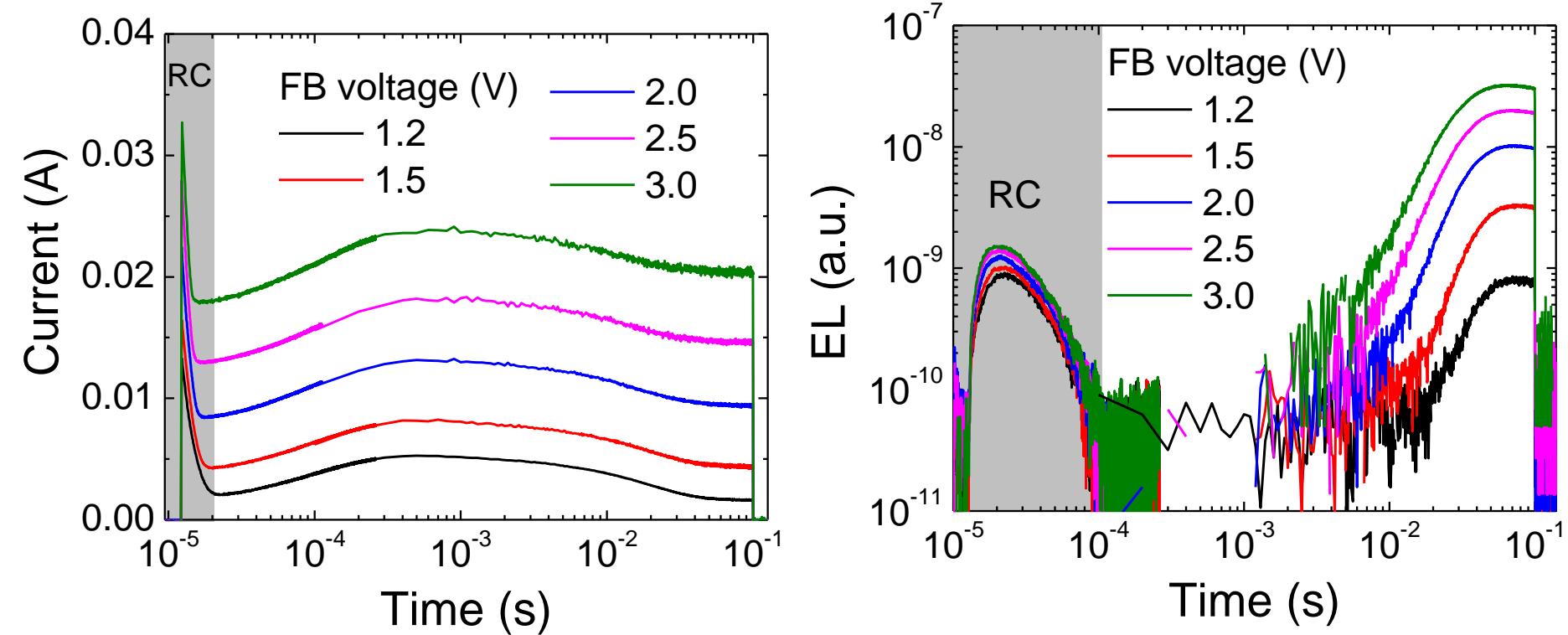




Q. Lin, Z. Wang, H. J. Snaith, M. B. Johnston,
L. M. Herz* et al., *Adv. Sci.* **5** (2018), 1700792

Z. Wang[#], Q. Lin[#], L. M. Herz, H. J. Snaith* et al., *Nature Energy*, **3** (2018), 855-861

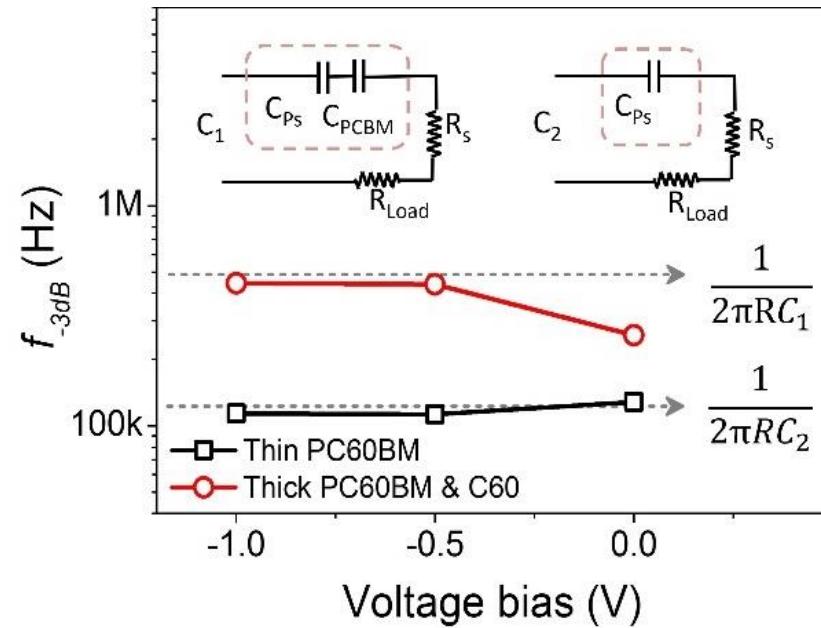
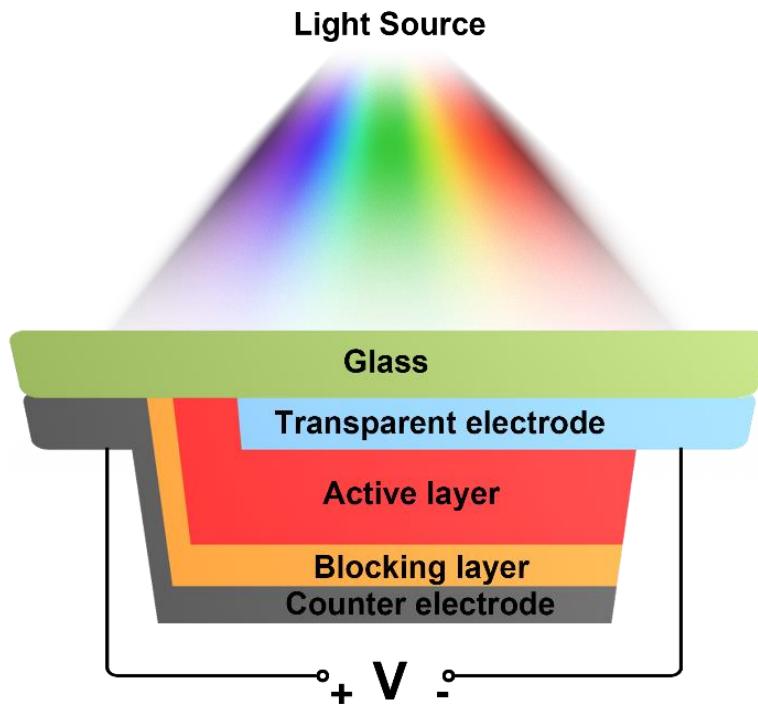
Light emitting diodes



Evaluation of ion migration within perovskites via double injection and transient EL

Q. Lin, *et al.*, unpublished work.

Jia Yang, Wangping Sheng, Ruiming Li, Lingyun Gong, Yanyan Li, Licheng Tan*, **Qianqian Lin***, Yiwang Chen*. Uncovering the mechanism of poly(ionic-liquid)s multiple inhibition of ion migration for efficient and stable perovskite solar cells. **Adv. Energy Mater.**, 12: 2103652 (2022).



Q. Lin *et al.*, **Adv. Mater.**, 27: 2060-2064 (2015).

Q. Lin *et al.*, **Nat. Photonics**, 9: 687–694 (2015), .

Q. Lin *et al.*, **Adv. Funct. Mater.** 27: 1702485 (2017).

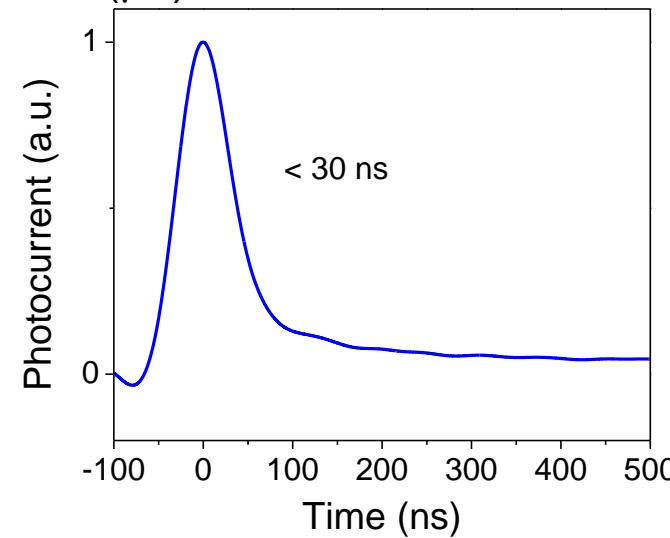
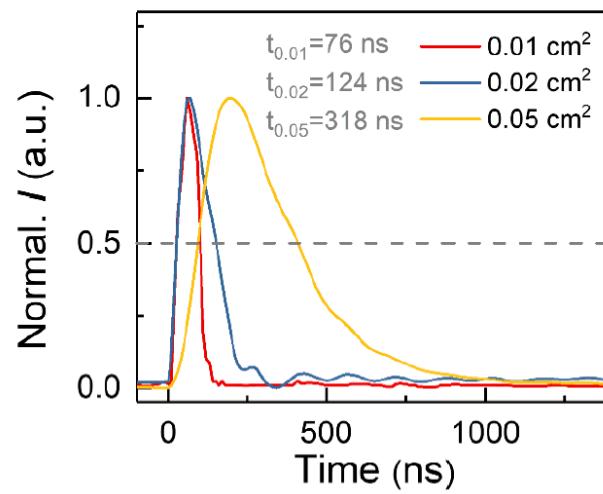
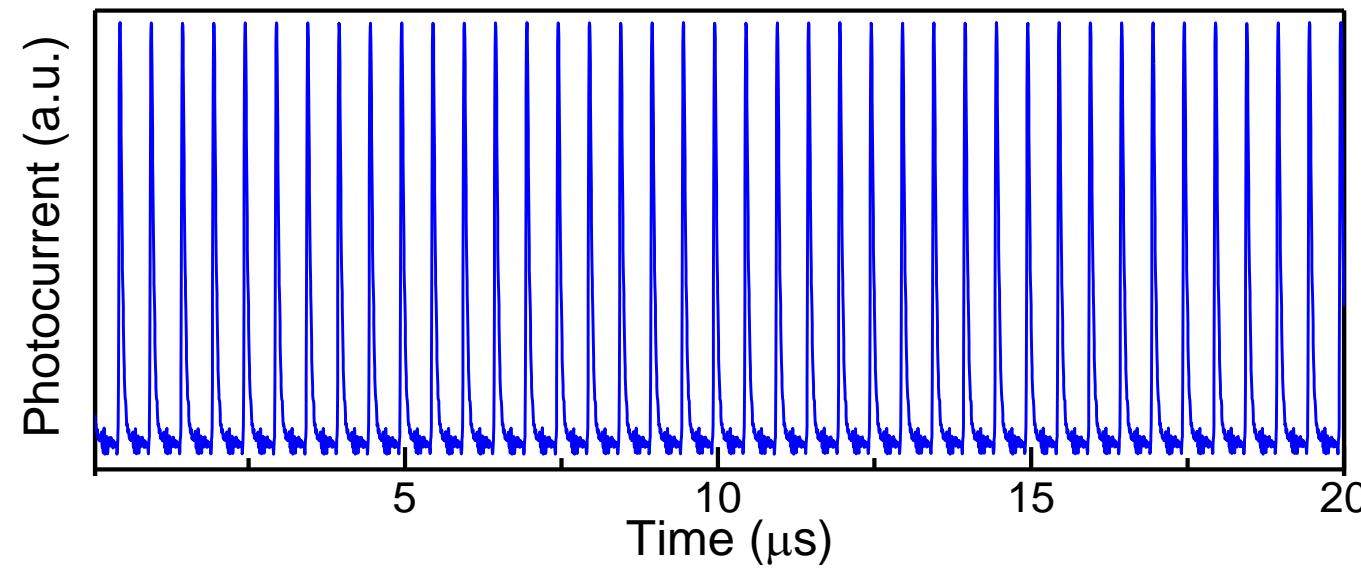
W. Li, L. Ding*, Q. Lin* *et al.*, **Adv. Funct. Mater.** 29: 1808948 (2019).

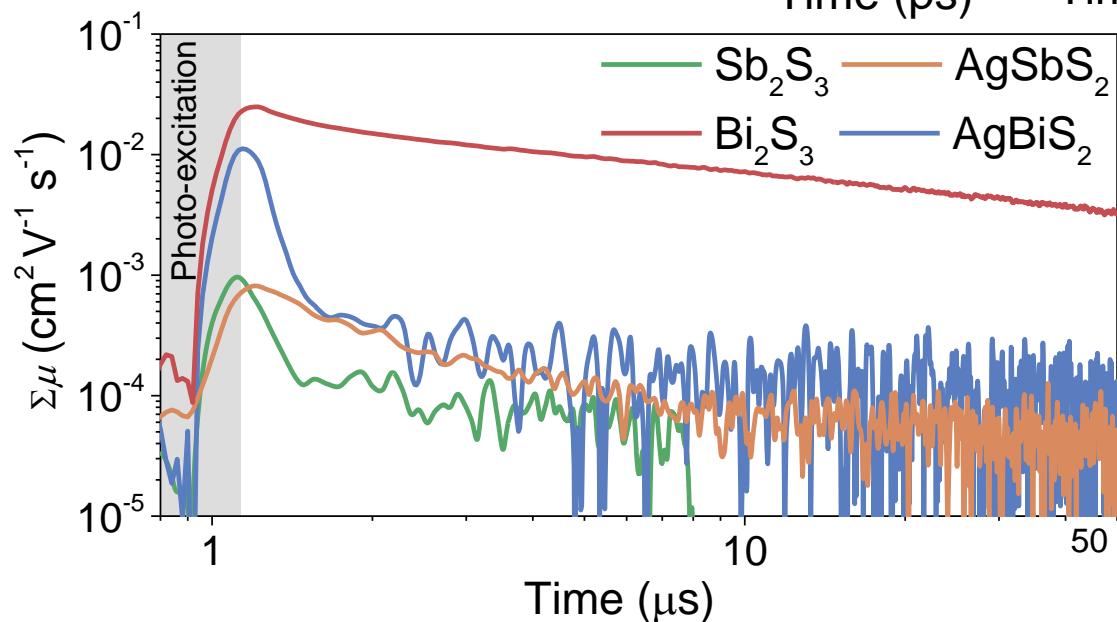
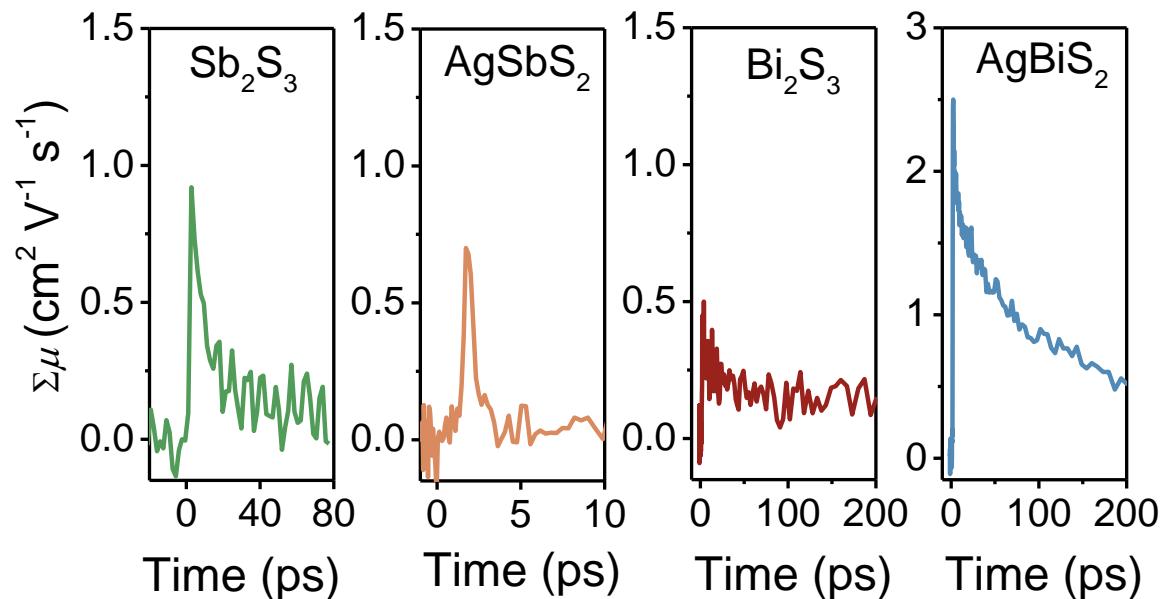
Y. Xu, Q. Lin* *et al.*, **Adv. Funct. Mater.** 33: 2212523 (2023).

$$f_{RC} = \frac{1}{2\pi RC} \quad C = \epsilon_0 \epsilon_r \frac{A}{d}$$

$$\frac{1}{f_{-3dB}^2} = \frac{1}{f_t^2} + \frac{1}{f_{RC}^2}$$

Is GHz bandwidth possible?

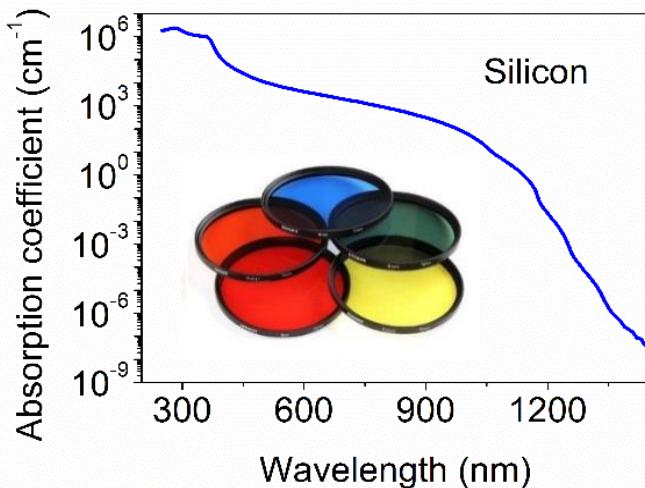




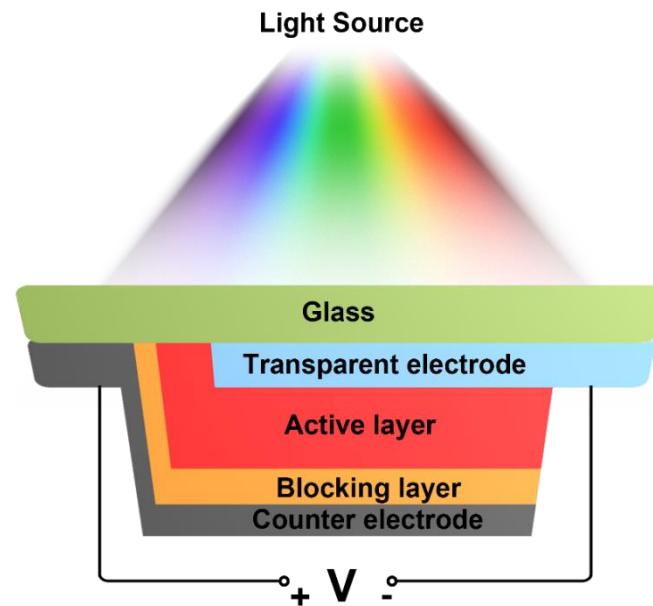
$$t_{tr} = \frac{d^2}{\mu * (V_{bi} - V_{bias})}$$

$$f_t = \frac{3.5}{2\pi t_{tr}}$$

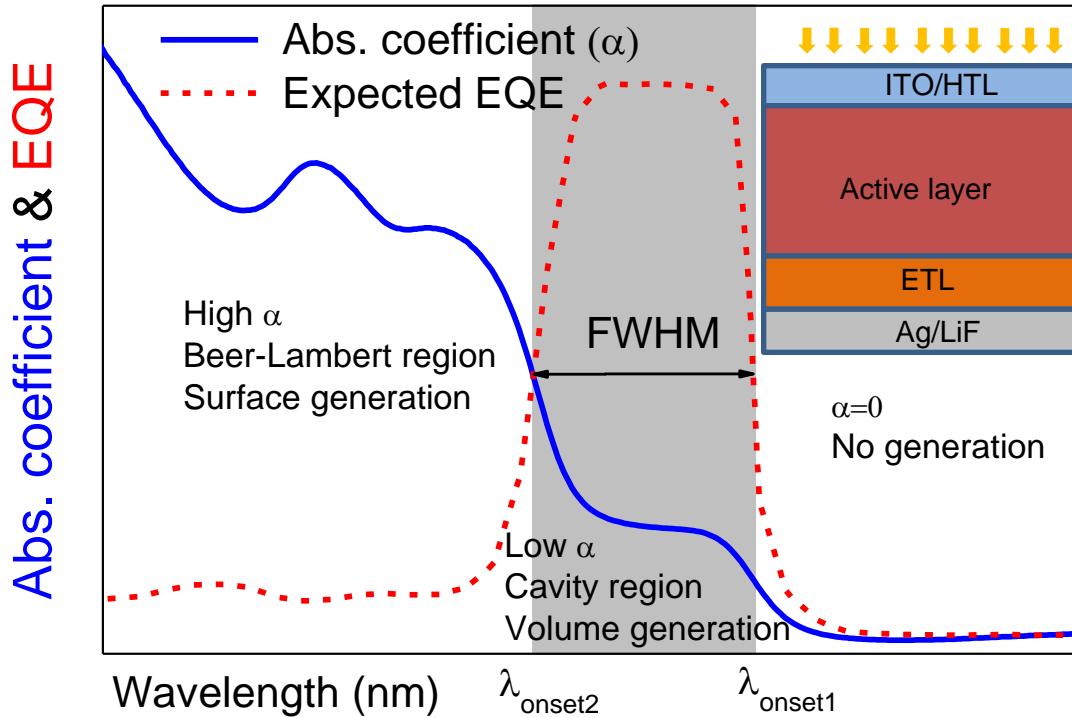
Filterless Photodetectors

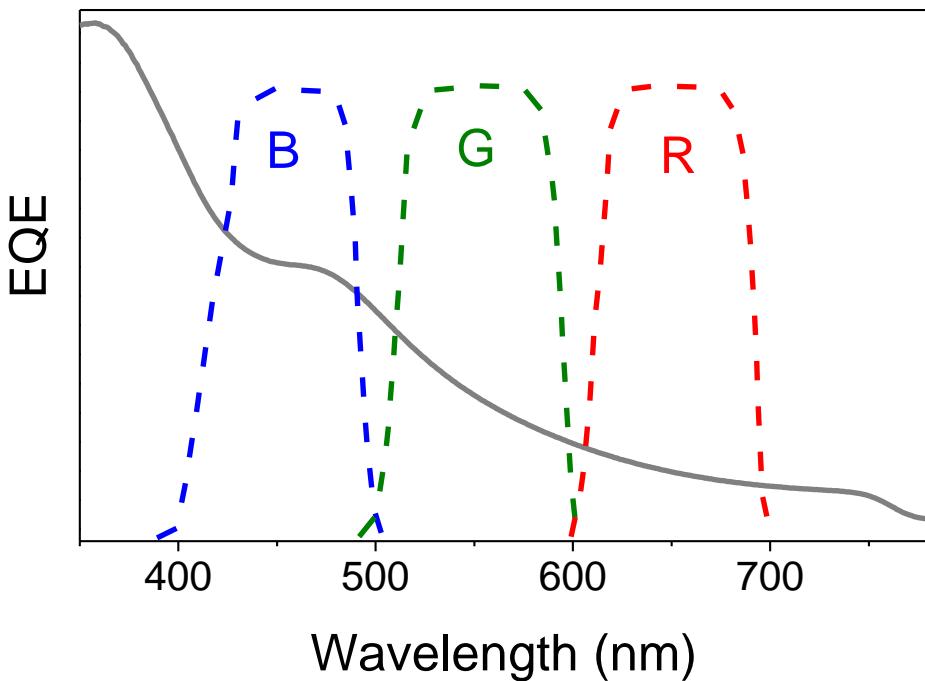


~10 million pixels
1.8 × 2.7 cm
~5 μm size
Filters

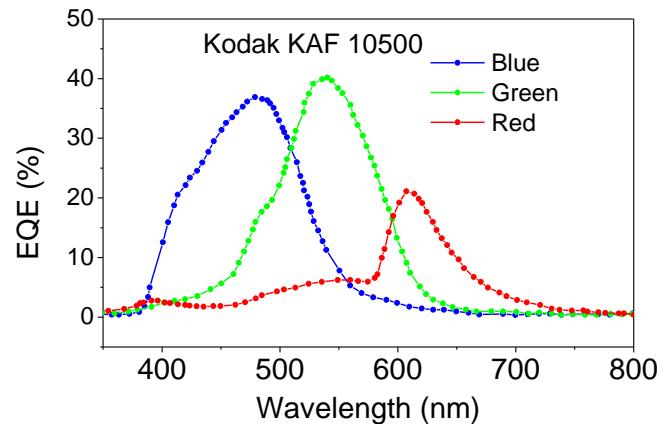
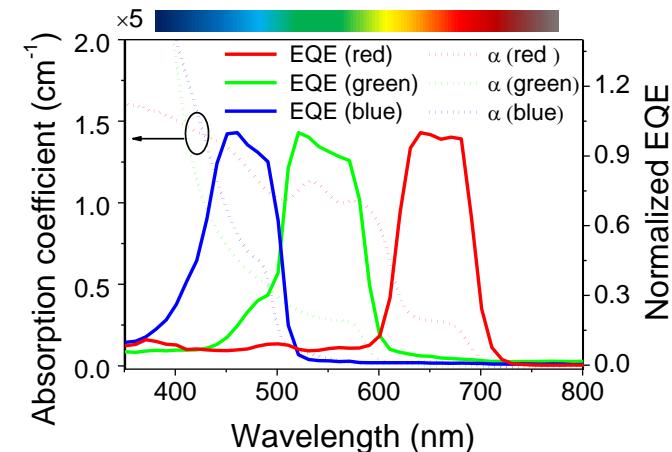


- ✓ Narrowband absorbers;
- ✓ Splitting the input light
- ✓ Charge collection narrowing (CCN).



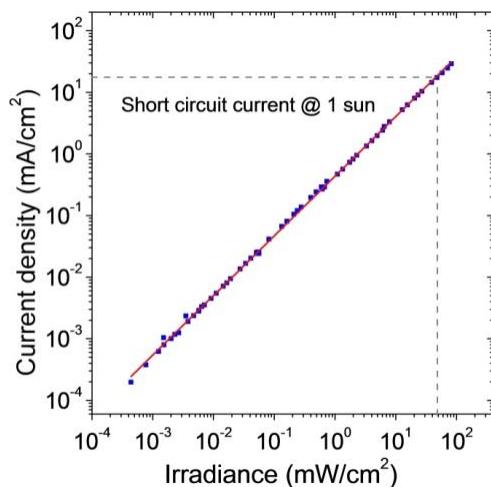
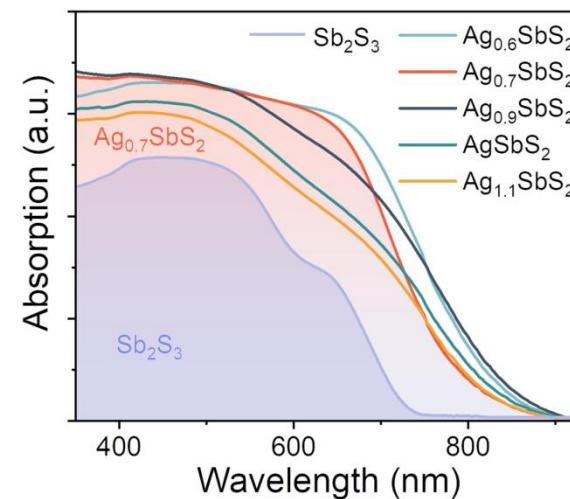
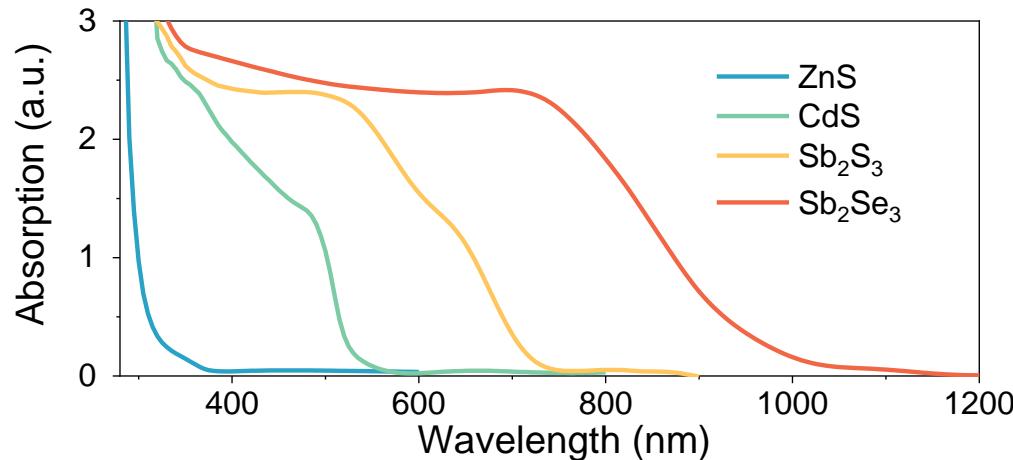


Realization of RGB detectors



A. Armin *et al.*, *Nature Comm.* **6**: 6343 (2015).

Q. Lin *et al.*, *Nature Photon.* **9**: 687–694 (2015).



Tunable bandgap

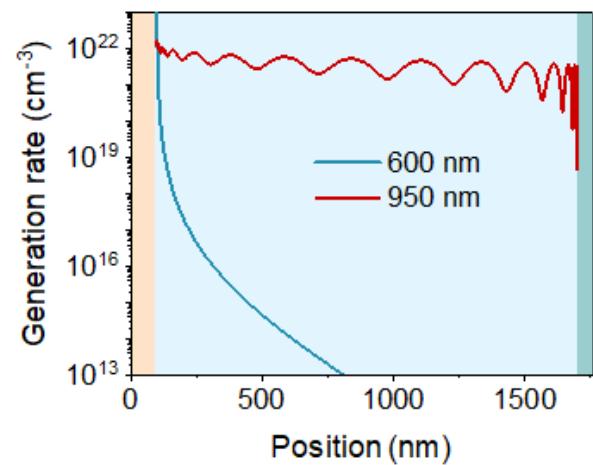
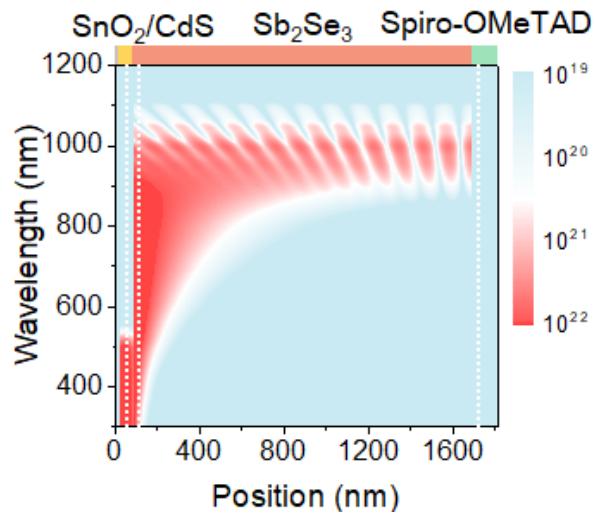
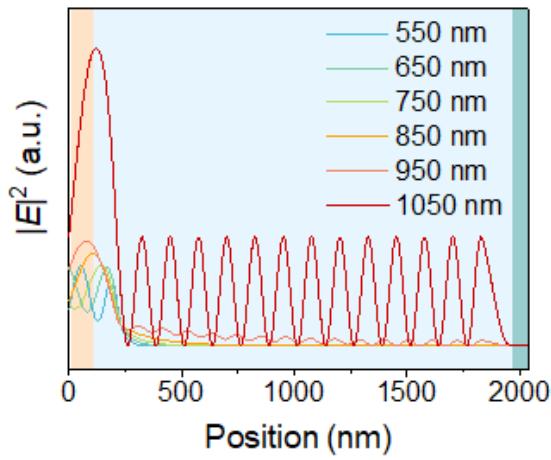
→ Spectral bandwidth

Low recombination

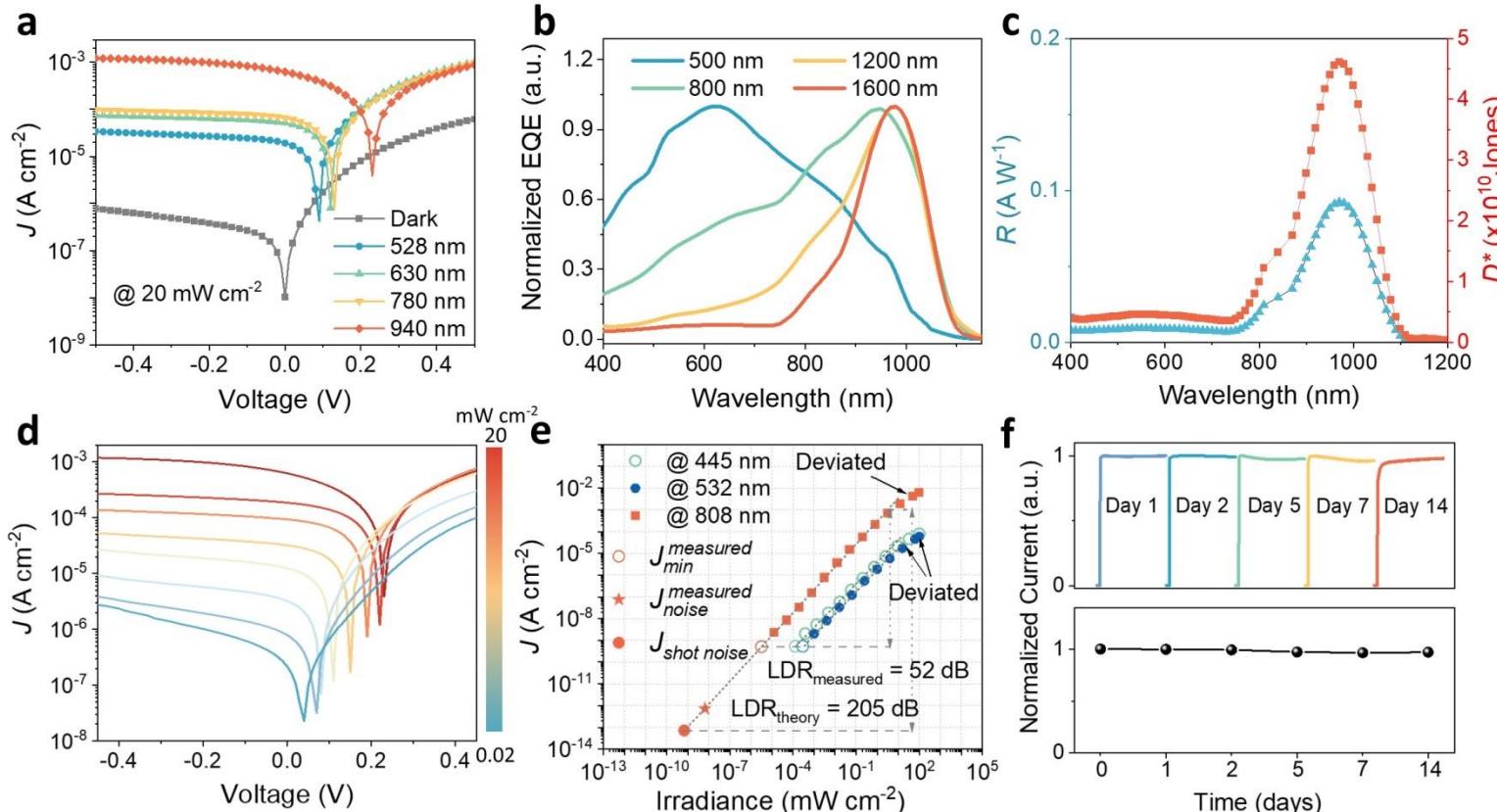
→ Large LDR

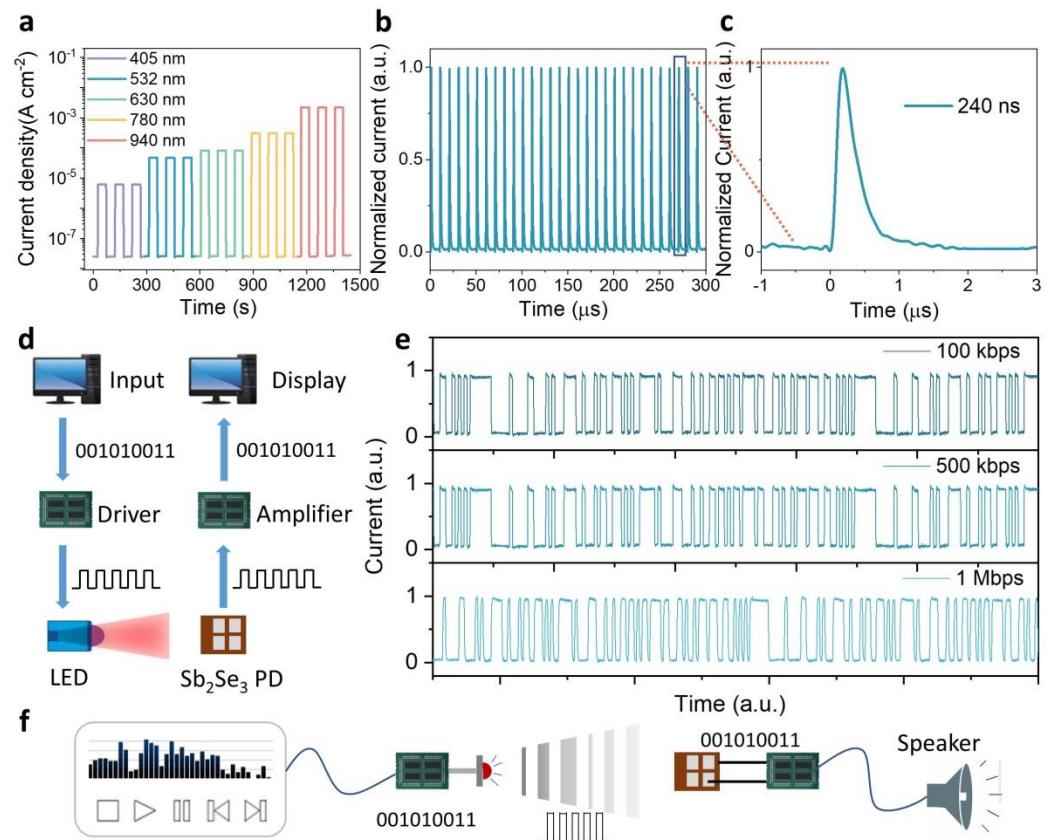
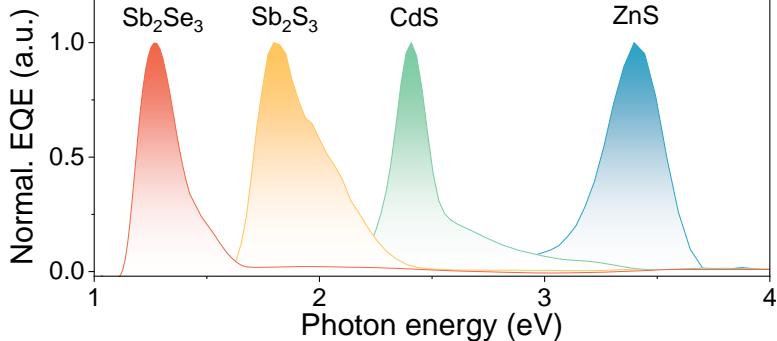
High mobility

→ Fast response

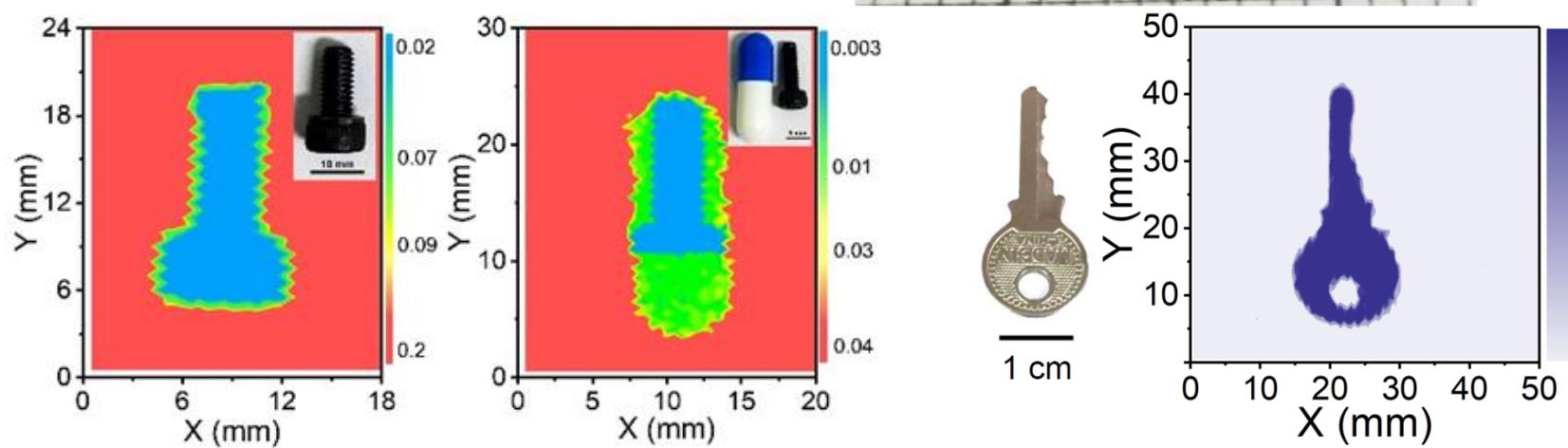
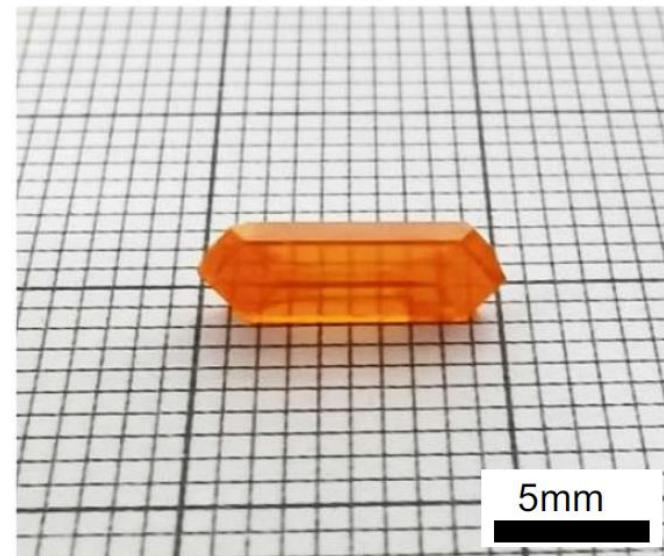
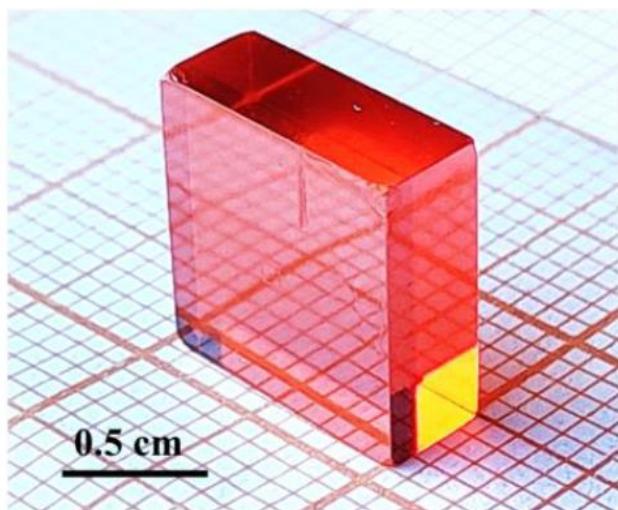


Proof of concept





Photodetection and Imaging 1

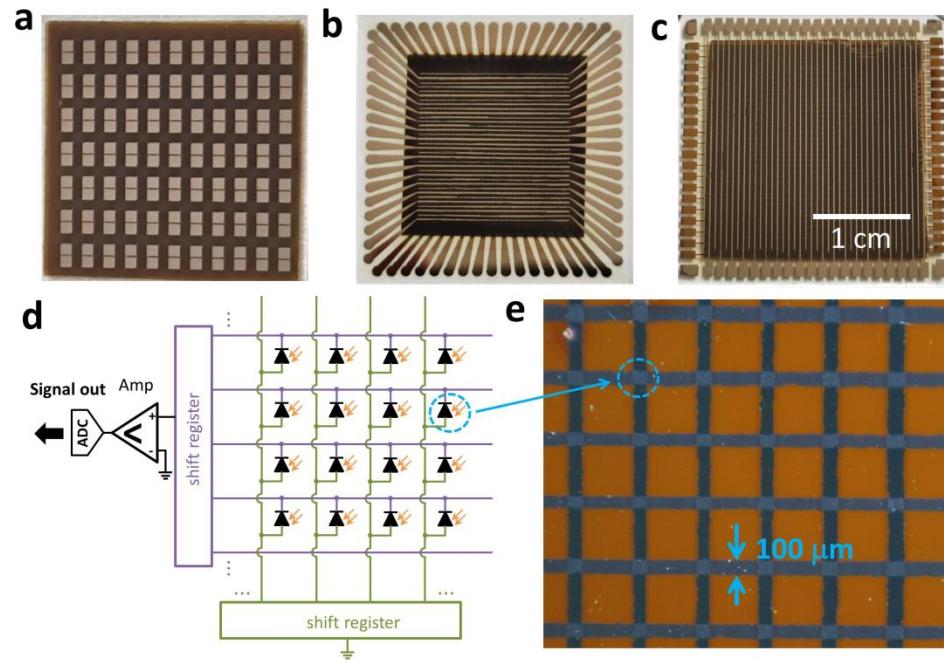


J. Peng, Q. Lin* et al., *Matter*, 5: 2251-2264 (2022).

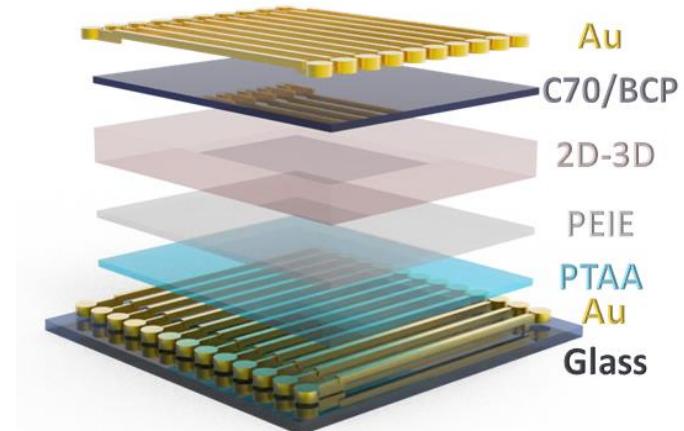
J. Peng, Q. Lin* et al., *Nat. Commun.*, 12: 1531 (2021).

F. Yao, C. Tao*, Q. Lin*, G. Fang* et al., *Nat. Commun.*, 11: 1194 (2020).

Photodetection and Imaging 2

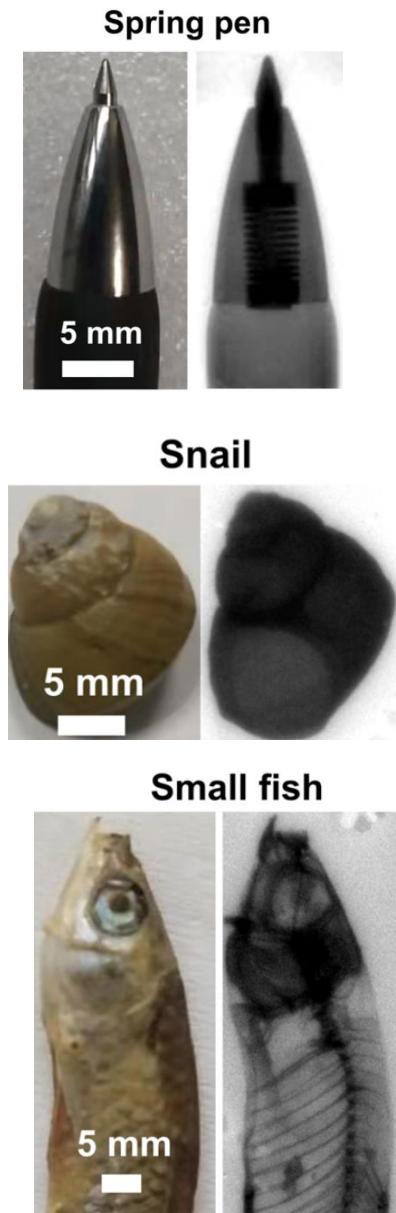
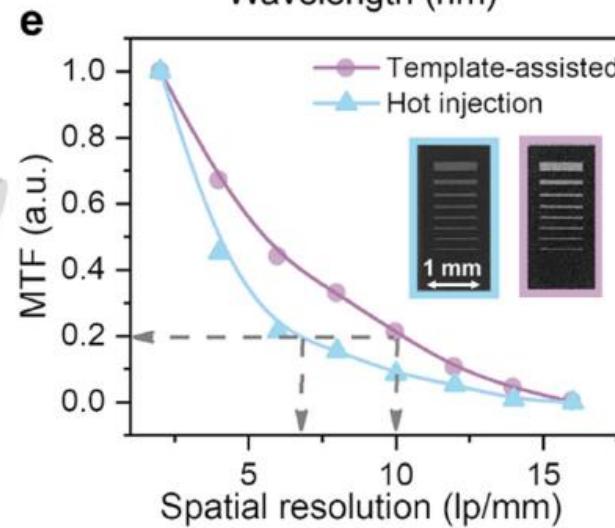
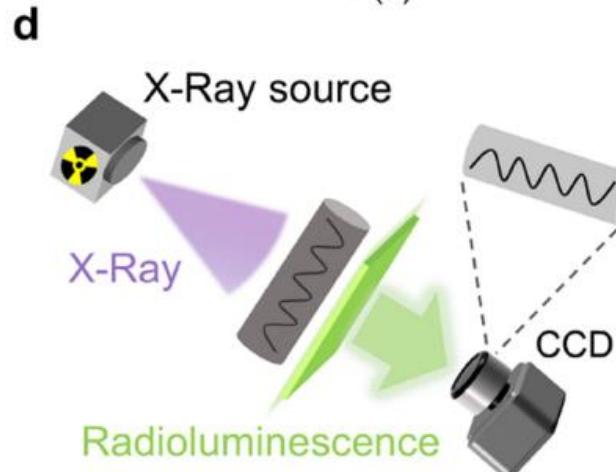
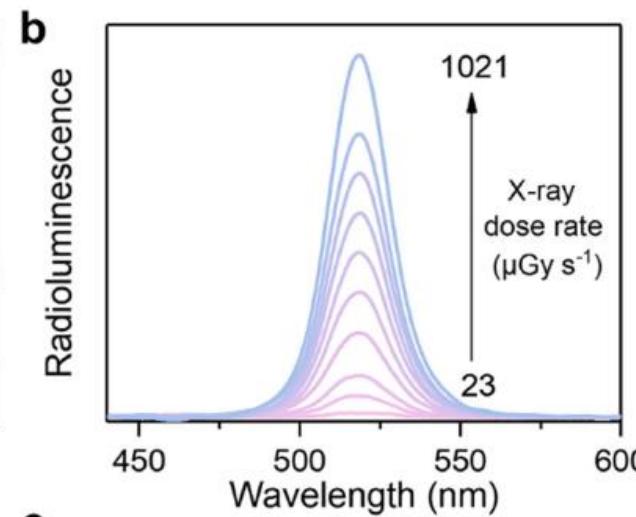
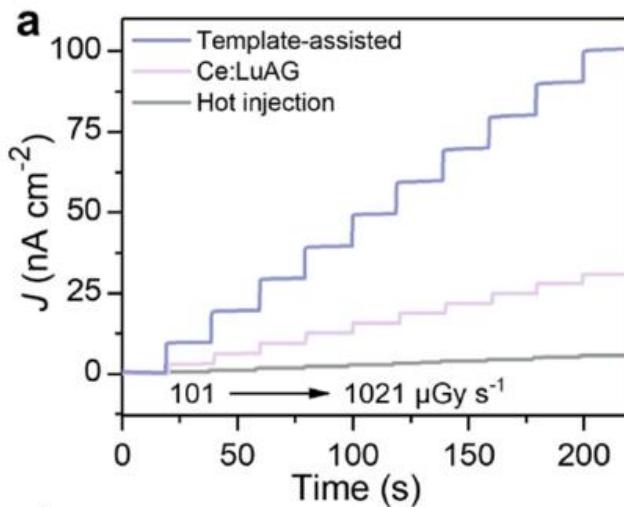


Photodetector array

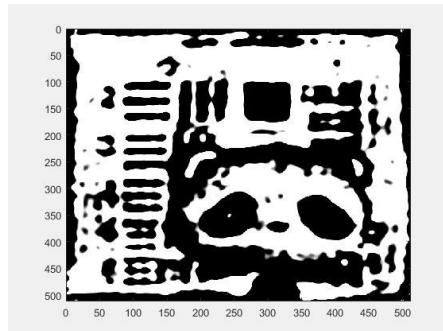
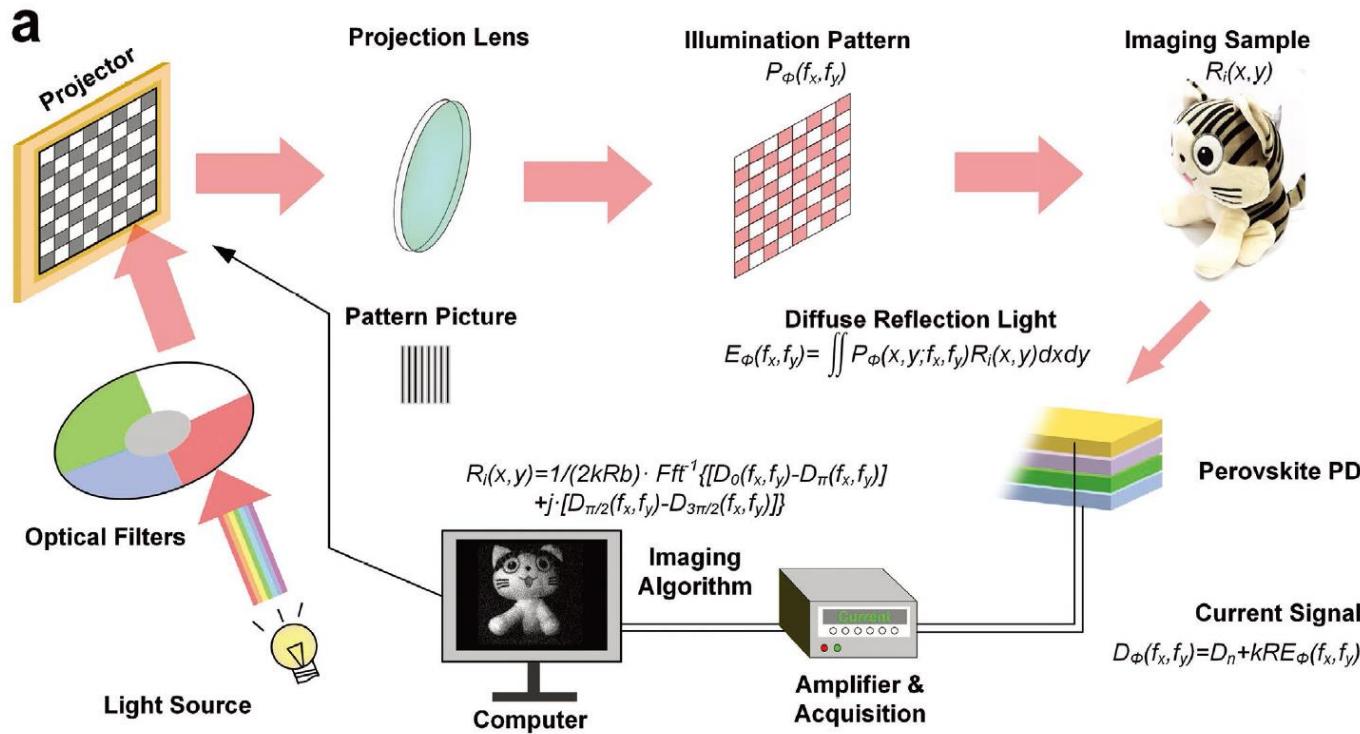


Structure of thin film photodiodes

Photodetection and Imaging 3

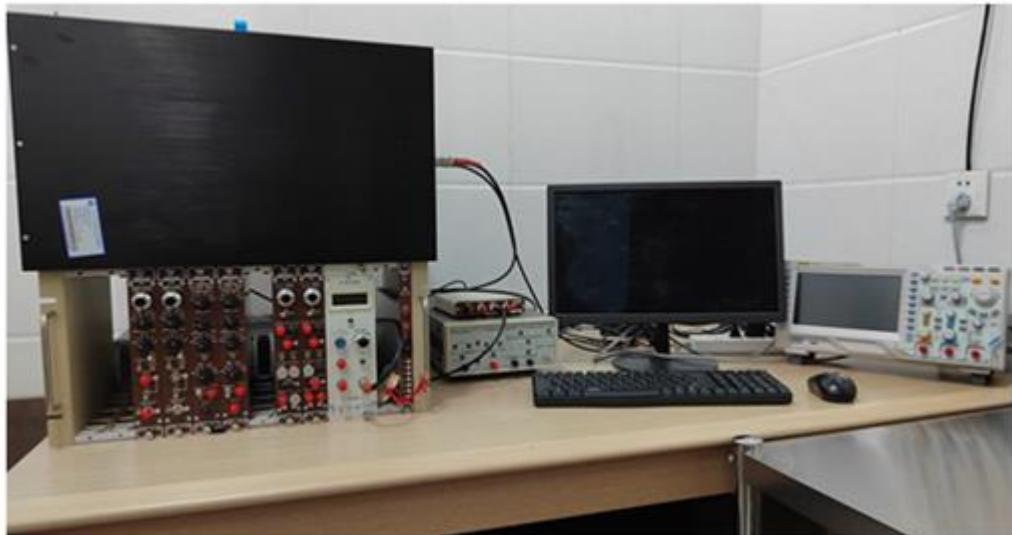


Photodetection and Imaging 4

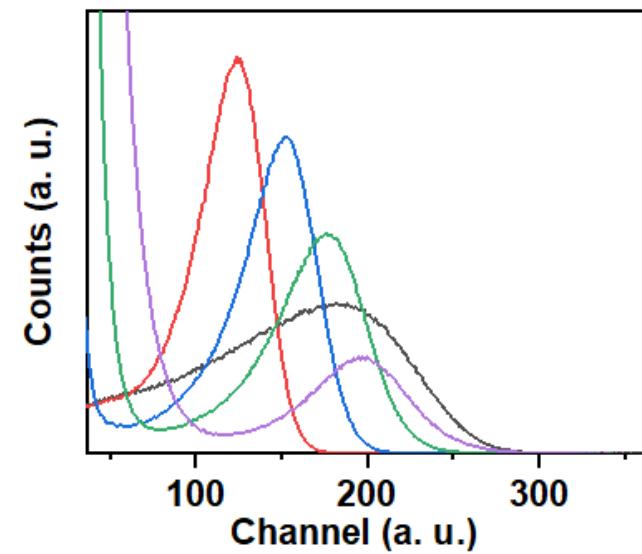
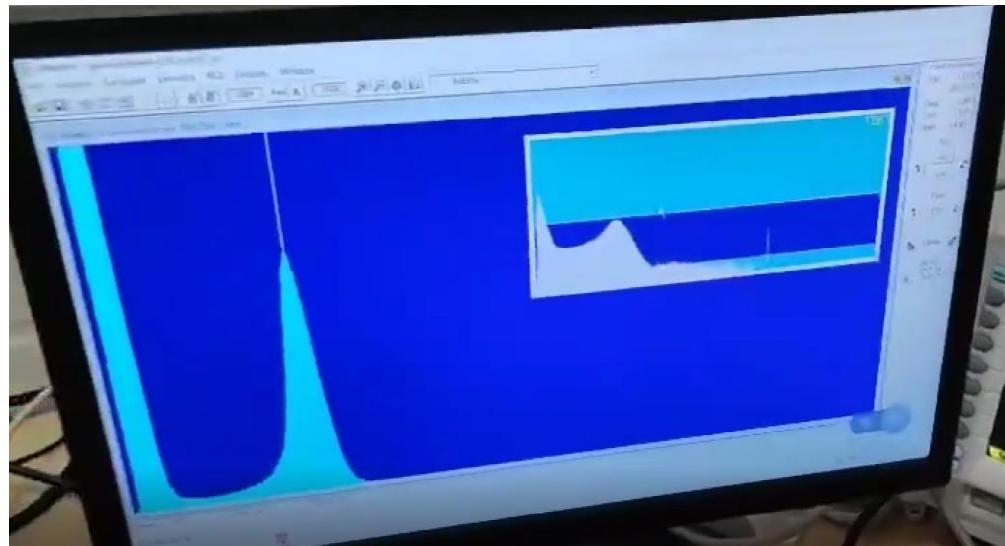
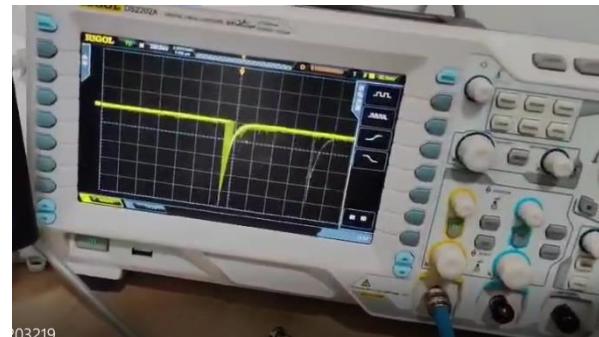


J. Zhong*, W. Mai* et al., *Adv. Funct. Mater.*, 2023, 11: 2023169.

S. Bai, Q. Lin* et al., *under review*.

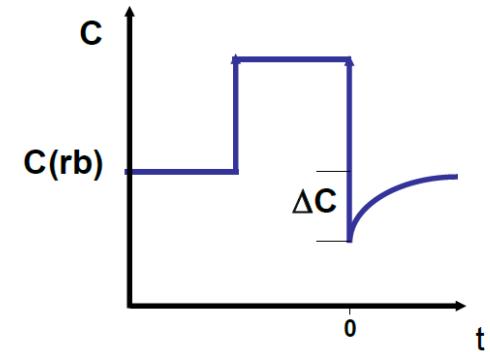
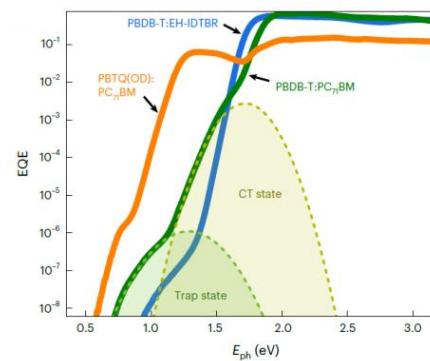
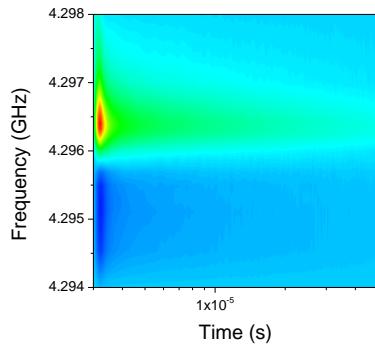


Single photon detection
of gamma-ray and neutrons



□ Opto-electronic property characterization:

TOC, CELIV, SCLC, IPC, DI, TREL, TRPL, TRMC, S-EQE, DLTS;



□ Opto-electronic strategies for device optimization:

Optical modeling, temporal response, spectral response.

Chapter 24: “Metal halide perovskites for photodetection” in the book *Wiley Series in Materials for Electronics and Optoelectronics: Photoconductivity and Photoconductive Materials*.





武汉大學

THANKS

